

Author Index

- Abukawa, T., see Shimomura, M. 237 (2004) 75
 Akimoto, K., see Mizuno, Y. 237 (2004) 40
 Akimoto, K., see Tajiri, H. 237 (2004) 645
 Akiyama, T., see Asano, K. 237 (2004) 206
 Anpo, M., see Yamashita, H. 237 (2004) 393
 Aoki, H., Design of electron correlation effects in interfaces and nanostructures 237 (2004) 2
 Aoyama, T., see Mizuno, Y. 237 (2004) 40
 Arafune, R., see Hayashi, K. 237 (2004) 296
 Araidai, M. and K. Watanabe, Ab initio study of field emission from hydrogen defects in diamond subsurfaces 237 (2004) 482
 Arokiaaraj, J., H.S. Djie and T. Mei, Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures 237 (2004) 256
 Aruga, T., see Hatta, S. 237 (2004) 270
 Asakura, K., see Niimi, H. 237 (2004) 641
 Asano, K., Y. Kangawa, H. Ishizaki, T. Akiyama, K. Nakamura and T. Ito, Theoretical investigations of adatom behavior on non-planar surfaces with GaAs(111)A 237 (2004) 206
 Azatyan, S., M. Hirai, M. Kusaka and M. Iwami, AES and STM investigations of room temperature Mn deposition onto Si(111) at different deposition rates 237 (2004) 105
 Baba, Y., T. Sekiguchi, I. Shimoyama and K.G. Nath, Structures of sub-monolayered silicon carbide films 237 (2004) 176
 Ban, S.H., see Shin, D.O. 237 (2004) 139
 Bao, X., X.S. Zhao, X. Li and J. Li, Pore structure characterization of large-pore periodic mesoporous organosilicas synthesized with varying SiO₂/template ratios 237 (2004) 380
 Berndt, R., see Limot, L. 237 (2004) 576
 Braun, W., see Herfort, J. 237 (2004) 181
 Cairney, J.M., see Ma, L.W. 237 (2004) 631
 Calster, A.V., see Siau, S. 237 (2004) 456
 Caudano, Y., see Humbert, C. 237 (2004) 462
 Caudano, Y., see Mani, A.A. 237 (2004) 444
 Caudano, Y., see Silien, C. 237 (2004) 477
 Champagne, B., see Mani, A.A. 237 (2004) 444
 Chaudhuri, A., see Shivaprasad, S.M. 237 (2004) 93
 Chia, P.A., see Gu, C. 237 (2004) 387
 Chiang, S., see Loui, A. 237 (2004) 559
 Chikalova-Luzina, O. and T. Matsumoto, Comparative analysis of the Si dangling bonds saturation by H or D in gas and liquid phases 237 (2004) 45
 Choi, H.-J., see Yoon, S. 237 (2004) 450
 Chu, Y.W., see Ho, H.Y. 237 (2004) 306
 Chun, M.-S., T. Teraji and T. Ito, Interfacial charge transfer and hole injection in α -NPD organic overlayer-CVD diamond substrate system 237 (2004) 469
 Chun, W.-J., see Niimi, H. 237 (2004) 641
 Chung, I., see Heo, J. 237 (2004) 593
 da Silva Jr., E.F., see Maia Jr., F.F. 237 (2004) 261
 da Silva Jr., E.F., see Sousa, J.S. 237 (2004) 553
 Daimon, H., see Guo, F.Z. 237 (2004) 616
 Daimon, H., see Hattori, A.N. 237 (2004) 311
 de Silva Jr., E.F., see de Sousa, J.S. 237 (2004) 548
 de Sousa, J.S., J.A.K. Freire, V.N. Freire and da Silva Jr., E.F., Differences of Stark shift behavior in Si/SiO₂ quantum wells and quantum dots 237 (2004) 548
 Diebold, U., L.V. Koplitz and O. Dulub, Atomic-scale properties of low-index ZnO surfaces 237 (2004) 336
 Djie, H.S., see Arokiaaraj, J. 237 (2004) 256
 Dreesen, L., see Humbert, C. 237 (2004) 462
 Dreesen, L., see Mani, A.A. 237 (2004) 444
 Dulub, O., see Diebold, U. 237 (2004) 336
 Edamoto, K., M. Sugihara, K. Ozawa and S. Otani, Oxidation process of Mo₂C(0001) studied by photoelectron spectroscopy 237 (2004) 498
 Edamoto, K., see Hasegawa, T. 237 (2004) 352
 Edamoto, K., see Sawada, K. 237 (2004) 343
 Enokida, T., see Sadoh, T. 237 (2004) 146
 Esmaelpour, M., see Ghorannevis, M. 237 (2004) 326
 Farias, D., W. Kamiński, J. Lobo, J. Ortega, E. Hulpke, R. Pérez, F. Flores and E.G. Michel, Phonon dynamics of the Sn/Ge(111)-(3 × 3) surface 237 (2004) 86
 Farias, G.A., see Maia Jr., F.F. 237 (2004) 261
 Farias, G.A., see Oliveira, C.L.N. 237 (2004) 266
 Flores, F., see Farias, D. 237 (2004) 86
 Freire, J.A.K., see de Sousa, J.S. 237 (2004) 548
 Freire, J.A.K., see Maia Jr., F.F. 237 (2004) 261
 Freire, J.A.K., see Oliveira, C.L.N. 237 (2004) 266

- Freire, V.N., see de Sousa, J.S. 237 (2004) 548
 Freire, V.N., see Maia, F.F. 237 (2004) 261
 Freire, V.N., see Oliveira, C.L.N. 237 (2004) 266
 Freire, V.N., see Sousa, J.S. 237 (2004) 553
 Fujikado, M., see Guo, F.Z. 237 (2004) 616
 Fujikado, M., see Hattori, A.N. 237 (2004) 311
 Fujimori, M., Y. Suwa, S. Heike, Y. Terada and T. Hashizume, Dihydride chain formation on a Si(1 0 0)-2 \times 1-H surface 237 (2004) 58
 Fujisawa, H., S. Shiraki, M. Nantoh and M. Kawai, Angle-resolved photoemission study of Co nanostructures on vicinal Au(111) surfaces 237 (2004) 291
 Fujisawa, H., see Shiraki, S. 237 (2004) 284
 Fujishiro, H.I., see Yagishita, Y. 237 (2004) 581
 Fujiwara, Y., see Yoshikane, T. 237 (2004) 246
 Fukaya, Y., A. Kawasuso, K. Hayashi and A. Ichimiya, Precise determination of surface Debye-temperature of Si(1 1 1)-7 \times 7 surface by reflection high-energy positron diffraction 237 (2004) 29
 Fukaya, Y., see Hayashi, K. 237 (2004) 34
 Fukaya, Y., see Shigeta, Y. 237 (2004) 21
 Fukuda, Y., see Liu, K.Z. 237 (2004) 627
 Fukuda, Y., see Shimomura, M. 237 (2004) 75
 Fukumoto, K., see Hattori, A.N. 237 (2004) 311
 Gazestani, S.H.H., M.G. Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy, Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel 237 (2004) 332
 Gewirth, A.A., see Mani, A.A. 237 (2004) 444
 Ghoranneviss, M., A.H. Sari, M. Esmaelpour, M.R. Hantehzadeh and H. Savaloni, Nitrogen implantation and heat treatment effect on the hardness improvement of the chromium film surface deposited on Si(1 1 1) substrate 237 (2004) 326
 Ghoranneviss, M., see Gazestani, S.H.H. 237 (2004) 332
 Ghoranneviss, M., see Sari, A.H. 237 (2004) 161
 Goto, T., see Shimomura, M. 237 (2004) 75
 Gotoh, Y., see Kawanowa, H. 237 (2004) 514
 Gotoh, Y., see Kondo, M. 237 (2004) 509
 Gotoh, Y., see Maehara, Y. 237 (2004) 316
 Gruznev, D.V., K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and K. Tatsuyama, Modification of Sb/Si(0 0 1) interface by incorporation of In(4 \times 3) surface reconstruction 237 (2004) 99
 Gu, C., P.A. Chia and X.S. Zhao, Doping of europium in the pores of surface-modified SBA-15 237 (2004) 387
 Gu, N., see Komiyama, M. 237 (2004) 503
 Gu, N., see Li, Y.-J. 237 (2004) 374
 Gunnella, R., see Shimomura, M. 237 (2004) 75
 Guo, F.Z., F. Matsui, M. Fujikado, T. Matsushita and H. Daimon, Stereoscopic photographs of atomic arrangements in MoS₂ single-crystal 237 (2004) 616
 Guo, F.Z., see Hattori, A.N. 237 (2004) 311
 Hama, K., see Ogata, K. 237 (2004) 348
 Hammer, L., see Heinz, K. 237 (2004) 519
 Han, C.-K., S.-B. Jung and H.-H. Park, Effects of tetraethoxysilane vapor treatment on the cetyltrimethylammonium bromide-templated silica mesoporous low- k thin film with 3D close-packed array of spherical pores 237 (2004) 405
 Hanada, T., see Mori, T. 237 (2004) 230
 Haneda, H., see Sakaguchi, I. 237 (2004) 358
 Hantehzadeh, M.R., see Gazestani, S.H.H. 237 (2004) 332
 Hantehzadeh, M.R., see Ghoranneviss, M. 237 (2004) 326
 Hantehzadeh, M.R., see Sari, A.H. 237 (2004) 161
 Hara, S., see Kubo, K. 237 (2004) 301
 Hasegawa, H., see Kotani, J. 237 (2004) 213
 Hasegawa, T., Y. Shirotori, K. Ozawa, K. Edamoto and K. Takahashi, Room temperature adsorption of NH₃ on Zn-terminated ZnO(0001) 237 (2004) 352
 Hashizume, T., see Fujimori, M. 237 (2004) 58
 Hashizume, T., see Kotani, J. 237 (2004) 213
 Hatta, S., H. Okuyama, M. Nishijima and T. Aruga, Fermi surface evolution and charge-density waves on In/Cu(001) 237 (2004) 270
 Hattori, A.N., M. Fujikado, T. Uchida, S. Okamoto, K. Fukumoto, F.Z. Guo, F. Matsui, K. Nakatani, T. Matsushita, K. Hattori and H. Daimon, Atomic structure of Fe thin-films on Cu(001) studied with stereoscopic photography 237 (2004) 311
 Hattori, K., see Hattori, A.N. 237 (2004) 311
 Hattori, T., see Hirose, K. 237 (2004) 411
 Hattori, T., see Nohira, H. 237 (2004) 134
 Hayashi, K., R. Arafune, S. Ueda and S. Ushioda, Spike structure in the very low energy photoelectron spectra of Ag(001) 237 (2004) 296
 Hayashi, K., see Fukaya, Y. 237 (2004) 29
 Hayashi, K., Y. Fukaya, A. Kawasuso and A. Ichimiya, Kinematical and dynamical analyses of reflection high-energy positron diffraction (RHEPD) patterns from Si(1 1 1) 7 \times 7 surfaces 237 (2004) 34
 Heike, S., see Fujimori, M. 237 (2004) 58
 Heinz, K., L. Hammer, A. Klein and A. Schmidt, Nanowire formation without surface steps 237 (2004) 519
 Heo, J., D. Kim, S.B. Park, T. Kim and I. Chung, Characterization of the electrical and magnetic properties of sub-micron MTJ cells using scanning probe microscope interfaced with an external magnetic field generator 237 (2004) 593
 Herfort, J., W. Braun, A. Trampert, H.-P. Schönherr and K.H. Ploog, Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(0 0 1) substrates 237 (2004) 181
 Hibino, H., Y. Homma, C.-W. Hu, M. Uwaha, T. Ogino and I.S.T. Tsong, Structural and morphological changes on surfaces with

- multiple phases studied by low-energy electron microscopy 237 (2004) 51
- Higai, S., see Nara, J. 237 (2004) 433
- Hill, R.H., see Park, H.-H. 237 (2004) 427
- Hino, T., see Taguchi, T. 237 (2004) 321
- Hirai, M., see Azatyan, S. 237 (2004) 105
- Hirai, M., see Kamezawa, C. 237 (2004) 611
- Hirai, M., see Labis, J. 237 (2004) 170
- Hirai, M., see Yagishita, Y. 237 (2004) 581
- Hirai, N., see Kubo, K. 237 (2004) 301
- Hirayama, Y., see Yamaguchi, H. 237 (2004) 649
- Hirohata, Y., see Taguchi, T. 237 (2004) 321
- Hirose, K., M. Yamawaki, K. Torii, T. Kawahara, S. Kawashiri and T. Hattori, Application of XPS time-dependent measurement to the analysis of charge trapping phenomena in HfAlO₂ films 237 (2004) 411
- Hirose, K., see Kobayashi, N. 237 (2004) 572
- Hirose, Y., see Nohira, H. 237 (2004) 134
- Hiruta, R., H. Kuribayashi, S. Shimizu, K. Sadoh and H. Iwasaki, Evolution of surface morphology of Si-trench sidewalls during hydrogen annealing 237 (2004) 63
- Hisadome, S., see Yoshikane, T. 237 (2004) 246
- Hishita, S., see Sakaguchi, I. 237 (2004) 358
- Ho, H.Y., C.W. Su, Y.W. Chu and C.S. Shern, Alloy formation of Ni ultrathin films on Pt(1 1 1) with Ag buffer layers 237 (2004) 306
- Hoffman, M.J., see Ma, L.W. 237 (2004) 631
- Hojo, D., see Tokuda, N. 237 (2004) 528
- Homma, Y., see Hibino, H. 237 (2004) 51
- Homma, Y., see Sumitomo, K. 237 (2004) 68
- Hora, H., see Sari, A.H. 237 (2004) 161
- Hosoi, Y., see Okamura, K. 237 (2004) 439
- Hpfl, R., see Sari, A.H. 237 (2004) 161
- Hu, C.-W., see Hibino, H. 237 (2004) 51
- Hulpke, E., see Farias, D. 237 (2004) 86
- Humbert, C., see Mani, A.A. 237 (2004) 444
- Humbert, C., Y. Caudano, L. Dreesen, Y. Sarthenaer, A.A. Mani, C. Silien, J.-J. Lemaire, P.A. Thiry and A. Peremans, Self-assembled organic and fullerene monolayers characterisation by two-colour SFG spectroscopy: a pathway to meet doubly resonant SFG process 237 (2004) 462
- Ichimiya, A., see Fukaya, Y. 237 (2004) 29
- Ichimiya, A., see Hayashi, K. 237 (2004) 34
- Ichimiya, A., see Mizuno, Y. 237 (2004) 40
- Iida, S., see Yukawa, M. 237 (2004) 156
- Ikeda, K., see Kawamura, K. 237 (2004) 621
- Ikeda, S., see Kiguchi, M. 237 (2004) 494
- Ikejima, Y., see Shimomura, M. 237 (2004) 75
- Imamura, M., see Tanaka, A. 237 (2004) 537
- Imanishi, A., see Nagai, T. 237 (2004) 532
- Inokuchi, K., see Soeno, T. 237 (2004) 543
- Inoue, K., see Yoshikane, T. 237 (2004) 246
- Inoue, M., see Ogata, K. 237 (2004) 348
- Ishii, H., see Okamura, K. 237 (2004) 439
- Ishii, H., see Shiraki, H. 237 (2004) 369
- Ishitani, T., see Ohya, K. 237 (2004) 606
- Ishizaki, H., see Asano, K. 237 (2004) 206
- Itakura, M., see Sadoh, T. 237 (2004) 146
- Itaya, K., see Shiraki, H. 237 (2004) 369
- Ito, T., K. Tsutsumida, K. Nakamura, Y. Kamegawa, K. Shiraishi, A. Taguchi and H. Kageshima, Systematic theoretical investigations of adsorption behavior on the GaAs(001)-(c(4 × 4)) surfaces 237 (2004) 194
- Ito, T., see Asano, K. 237 (2004) 206
- Ito, T., see Chun, M.-S. 237 (2004) 469
- Ito, T., see Tsujimoto, K. 237 (2004) 488
- Itoh, Y. and K. Ueda, Hydrogen and oxygen behaviors on Porous-Si surfaces observed using a scanning ESD ion microscope 237 (2004) 600
- Iwai, T. and G. Mizutani, Optical second harmonic spectroscopy of a Au(1 0 0) 5 × 20 reconstructed surface 237 (2004) 279
- Iwami, M., see Azatyan, S. 237 (2004) 105
- Iwami, M., see Kamezawa, C. 237 (2004) 611
- Iwami, M., see Labis, J. 237 (2004) 170
- Iwasaki, H., see Hiruta, R. 237 (2004) 63
- Iwasawa, Y., see Niimi, H. 237 (2004) 641
- Joumori, S., see Nakajima, K. 237 (2004) 416
- Jung, S.-B., see Han, C.-K. 237 (2004) 405
- Kageshima, H., see Ito, T. 237 (2004) 194
- Kamezawa, C., M. Hirai, M. Kusaka, M. Iwami and J. Labis, Surface analyses of Zr (film)/4H-SiC (substrate) by synchrotron radiation induced-PEEM 237 (2004) 611
- Kamiński, W., see Farias, D. 237 (2004) 86
- Kang, M.-G., see Yang, J.-K. 237 (2004) 251
- Kangawa, Y., see Asano, K. 237 (2004) 206
- Kangawa, Y., see Ito, T. 237 (2004) 194
- Katayama, M., see Kishida, M. 237 (2004) 110
- Kato, M., see Niimi, H. 237 (2004) 641
- Kawahara, T., see Hirose, K. 237 (2004) 411
- Kawai, M., see Fujisawa, H. 237 (2004) 291
- Kawai, M., see Shiraki, S. 237 (2004) 284
- Kawamura, K., K. Ikeda and M. Terauchi, A new method to characterize dopant profiles in NMOSFETs using conventional transmission electron microscopy 237 (2004) 621
- Kawanowa, H., M. Kondo, T. Shibata, Y. Gotoh and R. Souda, Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces 237 (2004) 514
- Kawanowa, H., see Kondo, M. 237 (2004) 509
- Kawanowa, H., see Maehara, Y. 237 (2004) 316
- Kawasaki, T., see Niimi, H. 237 (2004) 641
- Kawashiri, S., see Hirose, K. 237 (2004) 411
- Kawasuso, A., see Fukaya, Y. 237 (2004) 29
- Kawasuso, A., see Hayashi, K. 237 (2004) 34
- Kawata, H., see Mizuno, Y. 237 (2004) 40
- Kawata, H., see Tajiri, H. 237 (2004) 645
- Kawayama, I., see Misra, M. 237 (2004) 421
- Kenjo, A., see Sadoh, T. 237 (2004) 146

- Kiguchi, M., G. Yoshikawa, S. Ikeda and K. Saiki, Metal induced gap states at alkali halide/metal interface 237 (2004) 494
- Kim, D., see Heo, J. 237 (2004) 593
- Kim, H., see Yi, H. 237 (2004) 200
- Kim, T., see Heo, J. 237 (2004) 593
- Kim, W.S., see Yang, J.-K. 237 (2004) 251
- Kimura, K., see Nakajima, K. 237 (2004) 416
- Kimura, K., see Nohira, H. 237 (2004) 134
- Kimura, Y., see Okamura, K. 237 (2004) 439
- Kimura, Y., see Shiraki, H. 237 (2004) 369
- Kishida, M., A.A. Saranin, A.V. Zotov, V.G. Kotlyar, A. Nishida, Y. Murata, H. Okado, M. Katayama and K. Oura, Ti overlayers on Si(100) and their self-assembly induced by STM tip 237 (2004) 110
- Kitagawa, H., see Yukawa, M. 237 (2004) 156
- Kitajima, Y., see Niimi, H. 237 (2004) 641
- Kitano, K., see Nishi, R. 237 (2004) 654
- Kiwa, T., see Misra, M. 237 (2004) 421
- Klein, A., see Heinz, K. 237 (2004) 519
- Kobayashi, N., K. Hirose and M. Tsukada, First-principles calculation of field emission from adsorbed atom on metallic electrode 237 (2004) 572
- Kochiya, T., Y. Oyama, K. Suto and J.-Nishizawa, Anisotropy of lateral growth rate in liquid phase epitaxy of InP and its association with kink-step structures on the surface 237 (2004) 235
- Koike, K., see Ogata, K. 237 (2004) 348
- Koizumi, A., see Yoshikane, T. 237 (2004) 246
- Komiyama, M., see Li, Y.-J. 237 (2004) 374
- Komiyama, M., Y.-J. Li and N. Gu, In situ observations of tetraamineplatinum(II) hydroxide adsorption from its aqueous solution on heulandite (010) surface by atomic force microscopy 237 (2004) 503
- Komuro, T., see Ogata, K. 237 (2004) 348
- Kondo, M., H. Kawanowa, Y. Gotoh and R. Souda, Hydration of the HCl and NH₃ molecules adsorbed on amorphous water-ice surface 237 (2004) 509
- Kondo, M., see Kawanowa, H. 237 (2004) 514
- Kono, S., see Shimomura, M. 237 (2004) 75
- Kopitz, L.V., see Diebold, U. 237 (2004) 336
- Kotani, J., H. Hasegawa and T. Hashizume, Computer simulation of current transport in GaN and AlGaN Schottky diodes based on thin surface barrier model 237 (2004) 213
- Kotani, K., see Misra, M. 237 (2004) 421
- Kotlyar, V.G., see Kishida, M. 237 (2004) 110
- Kubo, K., N. Hirai and S. Hara, Decay of nano-islands on Au(100) electrode in sulfuric acid solution with Cl⁻ anions 237 (2004) 301
- Kuribayashi, H., see Hiruta, R. 237 (2004) 63
- Kuroiwa, T., see Nohira, H. 237 (2004) 134
- Kusaka, M., see Azatyan, S. 237 (2004) 105
- Kusaka, M., see Kamezawa, C. 237 (2004) 611
- Kusaka, M., see Labis, J. 237 (2004) 170
- Labis, J., J. Oh, H. Namatame, M. Taniguchi, M. Hirai, M. Kusaka and M. Iwami, High-resolution photoemission electron spectroscopy study on the oxynitridation of 6H-SiC(0001)- $\sqrt{3} \times \sqrt{3}R30^\circ$ surface 237 (2004) 170
- Labis, J., see Kamezawa, C. 237 (2004) 611
- Lavrinaitis, M.V., see Ryjkov, S.V. 237 (2004) 119
- Lee, N.-E., see Shin, D.O. 237 (2004) 139
- Lee, S., see Yi, H. 237 (2004) 200
- Lemaire, J.-J., see Humbert, C. 237 (2004) 462
- Li, J., see Bao, X. 237 (2004) 380
- Li, X., see Bao, X. 237 (2004) 380
- Li, Y.-J., see Komiyama, M. 237 (2004) 503
- Li, Y.-J., T. Matsumoto, N. Gu and M. Komiyama, Local structural change caused by light irradiation on TiO₂ (110) surface observed by scanning tunneling microscopy 237 (2004) 374
- Lifshits, V.G., see Gruznev, D.V. 237 (2004) 99
- Lifshits, V.G., see Ryjkov, S.V. 237 (2004) 119
- Limot, L. and R. Berndt, Kondo effect and surface-state electrons 237 (2004) 576
- Lin, F., see Sumitomo, K. 237 (2004) 68
- Liu, K.Z., Y. Suzuki and Y. Fukuda, AES and XPS studies of a GaP(0 0 1) surface treated by S₂Cl₂ and P₂S₅/(NH₄)₂S₂ 237 (2004) 627
- Lobo, J., see Farias, D. 237 (2004) 86
- Loui, A. and S. Chiang, Investigation of furan on vicinal Pd(111) by scanning tunneling microscopy 237 (2004) 559
- Ma, L.W., J.M. Cairney, M.J. Hoffman and P.R. Munroe, Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling 237 (2004) 631
- Maeda, F. and Y. Watanabe, Time-resolved core-level photoelectron spectroscopy and reflection high-energy electron diffraction study of surface phase transition on GaAs(0 0 1) 237 (2004) 224
- Maeda, K., Energy level broadening of defects causing nonideality in nearly ideal Si Schottky barriers 237 (2004) 165
- Maehara, Y., A. Yamada, H. Kawanowa and Y. Gotoh, Surface structures of Fe on Mo(110) surface investigated by RHEED 237 (2004) 316
- Maekawa, K., see Yamashita, H. 237 (2004) 393
- Maia Jr., F.F., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr., Interface properties in ZnSe/ZnS based strained superlattices and quantum wells 237 (2004) 261
- Makino, H., see Mori, T. 237 (2004) 230
- Mani, A.A., see Humbert, C. 237 (2004) 462
- Mani, A.A., Z.D. Schultz, B. Champagne, C. Humbert, L. Dreesen, A.A. Gewirth, J.O. White, P.A. Thiry, A. Peremans and Y. Caudano, Molecule orientation in self-assembled monolayers determined by infrared-visible sum-frequency generation spectroscopy 237 (2004) 444

- Maria Chong, A.S. and X.S. Zhao, Functionalized nanoporous silicas for the immobilization of penicillin acylase 237 (2004) 398
- Matsudaira, H., see Niimi, H. 237 (2004) 641
- Matsui, F., see Guo, F.Z. 237 (2004) 616
- Matsui, F., see Hattori, A.N. 237 (2004) 311
- Matsumoto, T., see Chikalova-Luzina, O. 237 (2004) 45
- Matsumoto, T., see Li, Y.-J. 237 (2004) 374
- Matsushita, T., see Guo, F.Z. 237 (2004) 616
- Matsushita, T., see Hattori, A.N. 237 (2004) 311
- Mei, T., see Arokiaaraj, J. 237 (2004) 256
- Michel, E.G., see Farias, D. 237 (2004) 86
- Miki, K., see Tokuda, N. 237 (2004) 528
- Misra, M., K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi, THz time domain spectroscopy of pulsed laser deposited BaTiO₃ thin films 237 (2004) 421
- Mitani, S., see Tsujimoto, K. 237 (2004) 488
- Mitsui, J., see Nohira, H. 237 (2004) 134
- Miura, T., T. Nakai and K. Yamaguchi, Atomically-controlled GaSb-termination of GaAs surface and its properties 237 (2004) 242
- Miyao, M., see Sadoh, T. 237 (2004) 146
- Miyashita, S., see Yamaguchi, H. 237 (2004) 649
- Miyazaki, T., see Saito, M. 237 (2004) 80
- Mizuki, J., see Takahashi, M. 237 (2004) 219
- Mizuno, Y., K. Akimoto, T. Aoyama, H. Suzuki, H. Nakahara, A. Ichimiya, K. Sumitani, T. Takahashi, X. Zhang, H. Sugiyama and H. Kawata, Structure of the Si(113) surface studied by surface X-ray diffraction 237 (2004) 40
- Mizutani, G., see Iwai, T. 237 (2004) 279
- Mori, M., see Gruznev, D.V. 237 (2004) 99
- Mori, T., T. Hanada, T. Morimura, K. Shin, H. Makino and T. Yao, Surface structure of InGaAs/InP(001) ordered alloy during and after growth 237 (2004) 230
- Morikawa, Y., see Nara, J. 237 (2004) 433
- Morimura, T., see Mori, T. 237 (2004) 230
- Morita, S., see Nishi, R. 237 (2004) 654
- Munroe, P.R., see Ma, L.W. 237 (2004) 631
- Murakami, H., see Misra, M. 237 (2004) 421
- Murakami, Y., see Sadoh, T. 237 (2004) 146
- Murata, Y., see Kishida, M. 237 (2004) 110
- Nagai, T., A. Imanishi and Y. Nakato, Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching 237 (2004) 532
- Nakagawa, K., see Nohira, H. 237 (2004) 134
- Nakahara, H., see Mizuno, Y. 237 (2004) 40
- Nakai, T., see Miura, T. 237 (2004) 242
- Nakajima, K., S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang, Characterization of HfO₂/Si(001) interface with high-resolution Rutherford backscattering spectroscopy 237 (2004) 416
- Nakajima, K., see Nohira, H. 237 (2004) 134
- Nakamura, K., see Asano, K. 237 (2004) 206
- Nakamura, K., see Ito, T. 237 (2004) 194
- Nakamura, M., see Nohira, H. 237 (2004) 134
- Nakao, H., see Yamashita, H. 237 (2004) 393
- Nakatake, M., see Sawada, K. 237 (2004) 343
- Nakatani, K., see Hattori, A.N. 237 (2004) 311
- Nakatani, S., see Tajiri, H. 237 (2004) 645
- Nakato, Y., see Nagai, T. 237 (2004) 532
- Nakatsuka, O., see Okada, E. 237 (2004) 150
- Namatame, H., see Labis, J. 237 (2004) 170
- Nantoh, M., see Fujisawa, H. 237 (2004) 291
- Nantoh, M., see Shiraki, S. 237 (2004) 284
- Nara, J., S. Higai, Y. Morikawa and T. Ohno, Adsorption structure of benzenethiol on Au(111): first-principles study 237 (2004) 433
- Nath, K.G., see Baba, Y. 237 (2004) 176
- Niimi, H., T. Tsutsumi, H. Matsudaira, T. Kawasaki, S. Suzuki, W.-J. Chun, M. Kato, Y. Kitajima, Y. Iwasawa and K. Asakura, Recent progress in energy-filtered high energy X-ray photoemission electron microscopy using a Wien filter type energy analyzer 237 (2004) 641
- Nishi, R., K. Kitano, I. Yi, Y. Sugawara and S. Morita, Phase detection method with positive-feedback control using a quartz resonator based atomic force microscope in a liquid environment 237 (2004) 654
- Nishida, A., see Kishida, M. 237 (2004) 110
- Nishijima, M., see Hatta, S. 237 (2004) 270
- Nishikawa, M., see Taguchi, T. 237 (2004) 321
- Nishizawa, J., see Kochiya, T. 237 (2004) 235
- Niwano, M., see Okamura, K. 237 (2004) 439
- Niwano, M., see Shiraki, H. 237 (2004) 369
- Nohira, H., T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori, Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400°C Sakai, W., see Nohira, H., Sakai, W., see H. Nohira, 237 (2004) 134
- Ogino, T., see Hibino, H. 237 (2004) 51
- Ogino, T., see Sumitomo, K. 237 (2004) 68
- Oh, J., see Labis, J. 237 (2004) 170
- Ohdomari, I., see Watanabe, T. 237 (2004) 125
- Ohmura, K., see Gruznev, D.V. 237 (2004) 99
- Ohno, T., see Nara, J. 237 (2004) 433
- Ohno, T., see Saito, M. 237 (2004) 80
- Ohya, K. and T. Ishitani, Monte Carlo study of secondary electron emission from SiO₂ induced by focused gallium ion beams 237 (2004) 606
- Oida, S., see Okada, E. 237 (2004) 150
- Okada, E., O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda, Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(1 0 0) 237 (2004) 150
- Okado, H., see Kishida, M. 237 (2004) 110

- Okamoto, S., see Hattori, A.N. 237 (2004) 311
- Okamura, K., Y. Hosoi, Y. Kimura, H. Ishii and M. Niwano, Adsorption of cata-condensed aromatics on a Si(1 0 0)-2 × 1 surface investigated by infrared absorption spectroscopy 237 (2004) 439
- Okuyama, H., see Hatta, S. 237 (2004) 270
- Oliveira, C.L.N., J.A.K. Freire, V.N. Freire and G.A. Farias, Effects of interfacial profiles on quantum levels in In_{0.5}Ga_{0.5}As/GaAs graded spherical quantum dots 237 (2004) 266
- Ono, S., see Shiraki, H. 237 (2004) 369
- Ortega, J., see Fariás, D. 237 (2004) 86
- Osipowicz, T., see Nakajima, K. 237 (2004) 416
- Osman, F., see Sari, A.H. 237 (2004) 161
- Otani, S., see Edamoto, K. 237 (2004) 498
- Oura, K., Preface 237 (2004) 1
- Ouri, K., see Kishida, M. 237 (2004) 110
- Oyama, Y., see Kochiya, T. 237 (2004) 235
- Ozawa, K., see Edamoto, K. 237 (2004) 498
- Ozawa, K., see Hasegawa, T. 237 (2004) 352
- Ozawa, K., see Sawada, K. 237 (2004) 343
- Paliwal, V.K., see Shivaprasad, S.M. 237 (2004) 93
- Park, H.-H., H.-H. Park and R.H. Hill, Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition 237 (2004) 427
- Park, H.-H., see Han, C.-K. 237 (2004) 405
- Park, H.-H., see Park, H.-H. 237 (2004) 427
- Park, H.-H., see Yang, J.-K. 237 (2004) 251
- Park, H.-H., see Yoon, S. 237 (2004) 450
- Park, S.B., see Heo, J. 237 (2004) 593
- Peremans, A., see Humbert, C. 237 (2004) 462
- Peremans, A., see Mani, A.A. 237 (2004) 444
- Ploog, K.H., see Herfort, J. 237 (2004) 181
- Pérez, R., see Fariás, D. 237 (2004) 86
- Ryjkov, S.V., M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits, Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition 237 (2004) 119
- Sadoh, T., Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao, Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSi-Ge]_n stacked structure 237 (2004) 146
- Saiki, K., see Kiguchi, M. 237 (2004) 494
- Saito, M., T. Ohno and T. Miyazaki, Magic layer thickness in Bi ultrathin films on Si(1 1 1) surface 237 (2004) 80
- Sakaguchi, I., S. Hishita and H. Haneda, Luminescence in Cu-implanted ZnO thin films 237 (2004) 358
- Sakai, A., see Okada, E. 237 (2004) 150
- Sakai, W., see Nohira, H. 237 (2004) 134
- Saranin, A.A., see Kishida, M. 237 (2004) 110
- Sardela, M.R., see Shin, D.O. 237 (2004) 139
- Sari, A.H., F. Osman, M. Ghoranneviss, H. Hora, R. Hpfl and M.R. Hantehzadeh, The effect of electron bombardment on optical properties of n-type silicon 237 (2004) 161
- Sari, A.H., see Ghoranneviss, M. 237 (2004) 326
- Sartenaer, Y., see Humbert, C. 237 (2004) 462
- Sasa, S., see Ogata, K. 237 (2004) 348
- Sasaki, M., see Sinsarp, A. 237 (2004) 587
- Sato, S., see Tanaka, A. 237 (2004) 537
- Savaloni, H., see Ghoranneviss, M. 237 (2004) 326
- Sawada, K., Y. Shirotori, K. Ozawa, K. Edamoto and M. Nakatake, Valence band structure of the ZnO (10 $\bar{1}$) Shirotori, Y., see Sawada, K. Shirotori, Y., see Sawada, K. 237 (2004) 343
- Sawano, K., see Nohira, H. 237 (2004) 134
- Schacht, E., see Siau, S. 237 (2004) 456
- Schmidt, A., see Heinz, K. 237 (2004) 519
- Schönherr, H.-P., see Herfort, J. 237 (2004) 181
- Schultz, Z.D., see Mani, A.A. 237 (2004) 444
- See, A., see Nakajima, K. 237 (2004) 416
- Sekiguchi, T., see Baba, Y. 237 (2004) 176
- Shahraki, M.G., see Gazestani, S.H.H.H. 237 (2004) 332
- Shern, C.S., see Ho, H.Y. 237 (2004) 306
- Shibata, T., see Kawanowa, H. 237 (2004) 514
- Shigeta, Y. and Y. Fukaya, Structural phase transition and thermal vibration of surface atoms studied by reflection high-energy electron diffraction 237 (2004) 21
- Shim, K.-H., see Shin, D.O. 237 (2004) 139
- Shimizu, S., see Hiruta, R. 237 (2004) 63
- Shimomura, M., Y. Ikejima, K. Yajima, T. Yagi, T. Goto, R. Gunnella, T. Abukawa, Y. Fukuda and S. Kono, Adsorption of thiophene on a Si(001)-2 × 1 surface studied by photoelectron spectroscopy and diffraction 237 (2004) 75
- Shimoyama, I., see Baba, Y. 237 (2004) 176
- Shin, D.O., M.R. Sardela, S.H. Ban, N.-E. Lee and K.-H. Shim, Strain relaxation of epitaxial CoSi₂ and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(001) and epi-CoSi₂/Si_{0.83}Ge_{0.17}/Si(001) structures 237 (2004) 139
- Shin, K., see Mori, T. 237 (2004) 230
- Shiraishi, K., see Ito, T. 237 (2004) 194
- Shiraishi, K., see Taguchi, A. 237 (2004) 189
- Shiraki, H., Y. Kimura, H. Ishii, S. Ono, K. Itaya and M. Niwano, Investigation of formation processes of an anodic porous alumina film on a silicon substrate 237 (2004) 369
- Shiraki, S., H. Fujisawa, M. Nantoh and M. Kawai, The growth of Fe, Ni and Co on vicinal Au(1 1 1) surfaces 237 (2004) 284
- Shiraki, S., see Fujisawa, H. 237 (2004) 291
- Shiraki, Y., see Nohira, H. 237 (2004) 134
- Shirotori, S., see Soeno, T. 237 (2004) 543
- Shirotori, Y., see Hasegawa, T. 237 (2004) 352
- Shirotori, Y., see Sawada, K. 237 (2004) 343
- Shivaprasad, S.M., V.K. Paliwal and A. Chaudhuri, The evolution of the Sb/Si interface at room temperature on the Si(111)-(7 × 7) and the Si(100)-(2 × 1) reconstructed surfaces 237 (2004) 93
- Shokouhy, A., see Gazestani, S.H.H.H. 237 (2004) 332

- Siau, S., A. Vervae, A.V. Calster, I. Swennen and E. Schacht, Influence of wet chemical treatments on the evolution of epoxy polymer layer surface roughness for use as a build-up layer 237 (2004) 456
- Silien, C., P.A. Thiry and Y. Caudano, Surface composition of K_2C_{60} multilayers and C603— monolayers investigated by high-resolution electron energy loss spectroscopy 237 (2004) 477
- Silien, C., see Humbert, C. 237 (2004) 462
- Sinsarp, A., Y. Yamada, M. Sasaki and S. Yamamoto, Local tunneling barrier height imaging of a reconstructed Pt(100) surface 237 (2004) 587
- Soeno, T., K. Inokuchi and S. Shiratori, Ultra-water-repellent surface: fabrication of complicated structure of SiO_2 nanoparticles by electrostatic self-assembled films 237 (2004) 543
- Song, W., see Yamauchi, Y. 237 (2004) 363
- Souda, R., see Kawanowa, H. 237 (2004) 514
- Souda, R., see Kondo, M. 237 (2004) 509
- Sousa, J.S., V.N. Freire and E.F. Silva, Conduction band anisotropy effects on the confined electron states of SiC/SiO_2 quantum dots 237 (2004) 553
- Su, C.W., see Ho, H.Y. 237 (2004) 306
- Sudoh, K., see Hiruta, R. 237 (2004) 63
- Sugawara, Y., see Nishi, R. 237 (2004) 654
- Sugihara, M., see Edamoto, K. 237 (2004) 498
- Sugiyama, H., see Mizuno, Y. 237 (2004) 40
- Sugiyama, H., see Tajiri, H. 237 (2004) 645
- Sumitani, K., see Mizuno, Y. 237 (2004) 40
- Sumitani, K., see Tajiri, H. 237 (2004) 645
- Sumitomo, K., F. Lin, Y. Homma and T. Ogino, Selective formation of Ge nanostructures on Si(111) surface with patterned steps 237 (2004) 68
- Suto, K., see Kochiya, T. 237 (2004) 235
- Suwa, Y., see Fujimori, M. 237 (2004) 58
- Suzuki, H., see Mizuno, Y. 237 (2004) 40
- Suzuki, M., see Nakajima, K. 237 (2004) 416
- Suzuki, M., see Nohira, H. 237 (2004) 134
- Suzuki, S., see Niimi, H. 237 (2004) 641
- Suzuki, Y., see Liu, K.Z. 237 (2004) 627
- Swennen, I., see Siau, S. 237 (2004) 456
- Tabuchi, M., see Yoshikane, T. 237 (2004) 246
- Taguchi, A. and K. Shiraishi, First-principles investigations of $GaAs(311)A$ surface reconstruction—failure of the electron counting model 237 (2004) 189
- Taguchi, A., see Ito, T. 237 (2004) 194
- Taguchi, T., Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa, Etching of polycrystalline copper by oblique injection of argon ion 237 (2004) 321
- Tajiri, H., K. Sumitani, S. Nakatani, T. Takahashi, K. Akimoto, H. Sugiyama, X. Zhang and H. Kawata, Sample holder assembly covering a wide range of temperatures for surface X-ray diffraction 237 (2004) 645
- Takahashi, K., see Hasegawa, T. 237 (2004) 352
- Takahashi, T., see Mizuno, Y. 237 (2004) 40
- Takahashi, T., see Tajiri, H. 237 (2004) 645
- Takahasi, M., Y. Yoneda and J. Mizuki, X-ray diffraction study on $GaAs(001)-2\times4$ surfaces under molecular-beam epitaxy conditions 237 (2004) 219
- Takeda, Y., see Tanaka, A. 237 (2004) 537
- Takeda, Y., see Yoshikane, T. 237 (2004) 246
- Tambo, T., see Gruznev, D.V. 237 (2004) 99
- Tanaka, A., Y. Takeda, M. Imamura and S. Sato, Femtosecond dynamic final-state effect in photoemission of surface-passivated metallic nanoparticles on graphite substrates 237 (2004) 537
- Taniguchi, M., see Labis, J. 237 (2004) 170
- Tatsumura, K., see Watanabe, T. 237 (2004) 125
- Tatsuyama, C., see Gruznev, D.V. 237 (2004) 99
- Terada, Y., see Fujimori, M. 237 (2004) 58
- Teraji, T., see Chun, M.-S. 237 (2004) 469
- Teraji, T., see Tsujimoto, K. 237 (2004) 488
- Terauchi, M., see Kawamura, K. 237 (2004) 621
- Thiry, P.A., see Humbert, C. 237 (2004) 462
- Thiry, P.A., see Mani, A.A. 237 (2004) 444
- Thiry, P.A., see Silien, C. 237 (2004) 477
- Toda, Y., see Yagishita, Y. 237 (2004) 581
- Tok, K.L., see Nakajima, K. 237 (2004) 416
- Tokuda, N., H. Watanabe, D. Hojo, S. Yamasaki, K. Miki and K. Yamabe, Fabrication of Cu nanowires along atomic step edge lines on $Si(111)$ substrates 237 (2004) 528
- Tonouchi, M., see Misra, M. 237 (2004) 421
- Torii, K., see Hirose, K. 237 (2004) 411
- Trampert, A., see Herfort, J. 237 (2004) 181
- Tsong, I.S.T., see Hibino, H. 237 (2004) 51
- Tsujimoto, K., S. Mitani, T. Teraji and T. Ito, Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films 237 (2004) 488
- Tsukada, M., see Kobayashi, N. 237 (2004) 572
- Tsukanov, D.A., see Ryjgov, S.V. 237 (2004) 119
- Tsuneyuki, S., see Yoshimoto, Y. 237 (2004) 274
- Tsutsumi, T., see Niimi, H. 237 (2004) 641
- Tsutsumida, K., see Ito, T. 237 (2004) 194
- Uchida, T., see Hattori, A.N. 237 (2004) 311
- Ueba, H., Elementary processes of vibrationally mediated motions of single adsorbed molecules 237 (2004) 565
- Ueda, K., Development of new X-ray microscopy using a low-energy electron beam 237 (2004) 636
- Ueda, K., see Itoh, Y. 237 (2004) 600
- Ueda, K., see Yoshimura, M. 237 (2004) 115
- Ueda, S., see Hayashi, K. 237 (2004) 296
- Urakami, A., see Yoshikane, T. 237 (2004) 246
- Ushioda, S., see Hayashi, K. 237 (2004) 296
- Uwaha, M., see Hibino, H. 237 (2004) 51
- Vervae, A., see Siau, S. 237 (2004) 456
- Watanabe, H., see Tokuda, N. 237 (2004) 528
- Watanabe, K., see Aradai, M. 237 (2004) 482

- Watanabe, K., see Yoshimura, M. 237 (2004) 115
- Watanabe, T., K. Tatsumura and I. Ohdomari, SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation 237 (2004) 125
- Watanabe, Y., see Maeda, F. 237 (2004) 224
- White, J.O., see Mani, A.A. 237 (2004) 444
- Woodruff, D.P., Understanding adsorbate bonding through quantitative surface structure determination 237 (2004) 13
- Yagi, T., see Shimomura, M. 237 (2004) 75
- Yagishita, Y., Y. Toda, M. Hirai and H.I. Fujishiro, Nano-scale patterning on sulfur terminated GaAs (001) surface by scanning tunneling microscope 237 (2004) 581
- Yajima, K., see Shimomura, M. 237 (2004) 75
- Yamabe, K., see Tokuda, N. 237 (2004) 528
- Yamada, A., see Maehara, Y. 237 (2004) 316
- Yamada, Y., see Sinsarp, A. 237 (2004) 587
- Yamaguchi, H., S. Miyashita and Y. Hirayama, Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers 237 (2004) 649
- Yamaguchi, K., see Miura, T. 237 (2004) 242
- Yamamoto, S., see Sinsarp, A. 237 (2004) 587
- Yamasaki, S., see Tokuda, N. 237 (2004) 528
- Yamashita, H., K. Maekawa, H. Nakao and M. Anpo, Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica 237 (2004) 393
- Yamauchi, Y., M. Yoshitake and W. Song, Surface study and thickness control of thin Al₂O₃ film on Cu-9%Al(111) single crystal 237 (2004) 363
- Yamauchi, Y., see Taguchi, T. 237 (2004) 321
- Yamawaki, M., see Hirose, K. 237 (2004) 411
- Yang, J.-K., M.-G. Kang, W.S. Kim and H.-H. Park, Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x (x = 0.5)/GaAs (0 0 1) system 237 (2004) 251
- Yang, J.-K., see Yoon, S. 237 (2004) 450
- Yano, M., see Ogata, K. 237 (2004) 348
- Yao, T., see Mori, T. 237 (2004) 230
- Yasuda, Y., see Okada, E. 237 (2004) 150
- Yi, H., S. Lee and H. Kim, Atomic geometry and theoretical scanning tunneling microscopy images of K chains on InAs(110) 237 (2004) 200
- Yi, I., see Nishi, R. 237 (2004) 654
- Yoneda, Y., see Takahashi, M. 237 (2004) 219
- Yoon, S., H.-J. Choi, J.-K. Yang and H.-H. Park, Comparative study between poly(*p*-phenylenevinylene) (PPV) and PPV/SiO₂ nanocomposite for interface with aluminum electrode 237 (2004) 450
- Yoshikane, T., A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda, Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy 237 (2004) 246
- Yoshikawa, G., see Kiguchi, M. 237 (2004) 494
- Yoshimoto, Y. and S. Tsuneyuki, First-principles study on the strain effect of the Cu(001)-c(2×2)N self-organized structure 237 (2004) 274
- Yoshimura, M., K. Watanabe and K. Ueda, Hydrogen interaction with Si(111) $\sqrt{3}\times\sqrt{3}$ -B surfaces 237 (2004) 115
- Yoshitake, M., see Yamauchi, Y. 237 (2004) 363
- Yoshitake, T., see Sadoh, T. 237 (2004) 146
- Yukawa, M., H. Kitagawa and S. Iida, Effect of an Ag buffer layer on a Cu/Ag/Si system 237 (2004) 156
- Zaima, S., see Okada, E. 237 (2004) 150
- Zhang, B.C., see Nakajima, K. 237 (2004) 416
- Zhang, X., see Mizuno, Y. 237 (2004) 40
- Zhang, X., see Tajiri, H. 237 (2004) 645
- Zhao, X.S., see Bao, X. 237 (2004) 380
- Zhao, X.S., see Gu, C. 237 (2004) 387
- Zhao, X.S., see Maria Chong, A.S. 237 (2004) 398
- Zheng, J.Z., see Nakajima, K. 237 (2004) 416
- Zotov, A.V., see Kishida, M. 237 (2004) 110

Subject Index

Alkali metals

- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- Atomic geometry and theoretical scanning tunneling microscopy images of K chains on InAs(110), H. Yi, S. Lee and H. Kim 237 (2004) 200
- Room temperature adsorption of NH_3 on Zn-terminated $\text{ZnO}(0001)$, T. Hasegawa, Y. Shirotori, K. Ozawa, K. Edamoto and K. Takahashi 237 (2004) 352

Alloys

- Quality of SiO_2 and of SiGe formed by oxidation of $\text{Si/Si}_{0.7}\text{Ge}_{0.3}$ heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- Alloy formation of Ni ultrathin films on Pt(111) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306
- Surface study and thickness control of thin Al_2O_3 film on Cu–9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363

Aluminium

- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- First-principles calculation of field emission from adsorbed atom on metallic electrode, N. Kobayashi, K. Hirose and M. Tsukada 237 (2004) 572
- Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers, H. Yamaguchi, S. Miyashita and Y. Hirayama 237 (2004) 649

Aluminium copper

- Surface study and thickness control of thin Al_2O_3 film on Cu–9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363

Aluminium oxide

- Surface study and thickness control of thin Al_2O_3 film on Cu–9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363
- Investigation of formation processes of an anodic porous alumina film on a silicon substrate, H. Shiraki, Y. Kimura, H. Ishii, S. Ono, K. Itaya and M. Niwano 237 (2004) 369

Ammonia

- Room temperature adsorption of NH_3 on Zn-terminated $\text{ZnO}(0001)$, T. Hasegawa, Y. Shirotori, K. Ozawa, K. Edamoto and K. Takahashi 237 (2004) 352
- Hydration of the HCl and NH_3 molecules adsorbed on amorphous water–ice surface, M. Kondo, H. Kawanowa, Y. Gotoh and R. Souda 237 (2004) 509

Annealing

- Evolution of surface morphology of Si-trench sidewalls during hydrogen annealing, R. Hiruta, H. Kuribayashi, S. Shimizu, K. Sudoh and H. Iwasaki 237 (2004) 63
- Modification of Sb/Si(001) interface by incorporation of In(4 × 3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- Strain relaxation of epitaxial CoSi_2 and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(001) and epi- CoSi_2 /Si_{0.83}Ge_{0.17}/Si(001) structures, D.O. Shin, M.R. Sardela Jr., S.H. Ban, N.-E. Lee and K.-H. Shim 237 (2004) 139

- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokianar, H.S. Djie and T. Mei 237 (2004) 256
- Antimony**
- The evolution of the Sb/Si interface at room temperature on the Si(111)-(7 × 7) and the Si(100)-(2 × 1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Modification of Sb/Si(001) interface by incorporation of In(4 × 3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers, H. Yamaguchi, S. Miyashita and Y. Hirayama 237 (2004) 649
- Arc evaporation**
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631
- Argon**
- Etching of polycrystalline copper by oblique injection of argon ion, T. Taguchi, Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa 237 (2004) 321
- Atomic force microscopy**
- Evolution of surface morphology of Si-trench sidewalls during hydrogen annealing, R. Hiruta, H. Kuribayashi, S. Shimizu, K. Sudoh and H. Iwasaki 237 (2004) 63
- Decay of nano-islands on Au(100) electrode in sulfuric acid solution with Cl⁻ anions, K. Kubo, N. Hirai and S. Hara 237 (2004) 301
- Etching of polycrystalline copper by oblique injection of argon ion, T. Taguchi, Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa 237 (2004) 321
- Comparative study between poly(*p*-phenylene-vinylene) (PPV) and PPV/SiO₂ nano-composite for interface with aluminum electrode, S. Yoon, H.-J. Choi, J.-K. Yang and H.-H. Park 237 (2004) 450
- Influence of wet chemical treatments on the evolution of epoxy polymer layer surface roughness for use as a build-up layer, S. Siau, A. Vervae, A.V. Calster, I. Swennen and E. Schacht 237 (2004) 456
- In situ observations of tetraamineplatinum(II) hydroxide adsorption from its aqueous solution on heulandite (010) surface by atomic force microscopy, M. Komiyama, Y.-J. Li and N. Gu 237 (2004) 503
- Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching, T. Nagai, A. Imanishi and Y. Nakato 237 (2004) 532
- Ultra-water-repellent surface: fabrication of complicated structure of SiO₂ nanoparticles by electrostatic self-assembled films, T. Soeno, K. Inokuchi and S. Shiratori 237 (2004) 543
- Auger electron spectroscopy**
- AES and STM investigations of room temperature Mn deposition onto Si(111) at different deposition rates, S. Azatyan, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 105
- Alloy formation of Ni ultrathin films on Pt(111) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306
- Surface study and thickness control of thin Al₂O₃ film on Cu-9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363
- Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching, T. Nagai, A. Imanishi and Y. Nakato 237 (2004) 532
- AES and XPS studies of a GaP(001) surface treated by S₂Cl₂ and P₂S₅/(NH₄)₂S₂, K.Z. Liu, Y. Suzuki and Y. Fukuda 237 (2004) 627
- Band structure**
- Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x (x = 0.5)/GaAs(001) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park 237 (2004) 251
- Valence band structure of the ZnO(1010) surface studied by angle-resolved photoemission spectroscopy, K. Sawada, Y. Shiratori, K. Ozawa, K. Edamoto and M. Nakatake 237 (2004) 343
- Conduction band anisotropy effects on the confined electron states of SiC/SiO₂ quantum dots, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 237 (2004) 553

Barium

- THz time domain spectroscopy of pulsed laser deposited BaTiO₃ thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421

Biological materials

- Functionalized nanoporous silicas for the immobilization of penicillin acylase, A.S. Maria Chong and X.S. Zhao 237 (2004) 398

Boron

- Hydrogen interaction with Si(1 1 1) $\sqrt{3}\times\sqrt{3}$ -B surfaces, M. Yoshimura, K. Watanabe and K. Ueda 237 (2004) 115

Cadolinium

- Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x ($\alpha = 0.5$)/GaAs (0 0 1) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park 237 (2004) 251

Carbides

- Oxidation process of Mo₂C(0 0 1) studied by photoelectron spectroscopy, K. Edamoto, M. Sugihara, K. Ozawa and S. Otani 237 (2004) 498

Carbon

- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(1 0 0), E. Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150

Catalysis

- In situ observations of tetraamineplatinum(II) hydroxide adsorption from its aqueous solution on heulandite (0 1 0) surface by atomic force microscopy, M. Komiyama, Y.-J. Li and N. Gu 237 (2004) 503

Chemical vapour deposition

- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488

Cobalt

- Strain relaxation of epitaxial CoSi₂ and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(0 0 1) and epi-CoSi₂/Si_{0.83}Ge_{0.17}/Si(0 0 1) structures, D.O. Shin, M.R. Sardela Jr., S.H. Ban, N.-E. Lee and K.-H. Shim 237 (2004) 139
- The growth of Fe, Ni and Co on vicinal Au(1 1 1) surfaces, S. Shiraki, H. Fujisawa, M. Nantoh and M. Kawai 237 (2004) 284
- Kondo effect and surface-state electrons, L. Limot and R. Berndt 237 (2004) 576

Computer simulation

- Theoretical investigations of adatom behavior on non-planar surfaces with GaAs(*n* 1 1)A, K. Asano, Y. Kangawa, H. Ishizaki, T. Akiyama, K. Nakamura and T. Ito 237 (2004) 206
- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Gholipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy 237 (2004) 332
- First-principles calculation of field emission from adsorbed atom on metallic electrode, N. Kobayashi, K. Hirose and M. Tsukada 237 (2004) 572

Copper

- Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida 237 (2004) 156
- Atomic structure of Fe thin-films on Cu(0 0 1) studied with stereoscopic photography, A.N. Hattori, M. Fujikado, T. Uchida, S. Okamoto, K. Fukumoto, F.Z. Guo, F. Matsui, K. Nakatani, T. Matsushita, K. Hattori and H. Daimon 237 (2004) 311
- Etching of polycrystalline copper by oblique injection of argon ion, T. Taguchi, Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa 237 (2004) 321
- Luminescence in Cu-implanted ZnO thin films, I. Sakaguchi, S. Hishita and H. Haneda 237 (2004) 358

Depth profiling

- Alloy formation of Ni ultrathin films on Pt(1 1 1) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306
- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Gholipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy 237 (2004) 332
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and

- CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514
- Deuterium**
- Comparative analysis of the Si dangling bonds saturation by H or D in gas and liquid phases, O. Chikalova-Luzina and T. Matsumoto 237 (2004) 45
- Diamond**
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488
- Doping effects**
- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Electrical properties**
- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- Characterization of the electrical and magnetic properties of sub-micron MTJ cells using scanning probe microscope interfaced with an external magnetic field generator, J. Heo, D. Kim, S.B. Park, T. Kim and I. Chung 237 (2004) 593
- Electron bombardment**
- The effect of electron bombardment on optical properties of n-type silicon, A.H. Sari, F. Osman, M. Ghoranneviss, H. Hora, R. Hpfel and M.R. Hantehzadeh 237 (2004) 161
- Electron diffraction**
- Structural phase transition and thermal vibration of surface atoms studied by reflection high-energy electron diffraction, Y. Shigeta and Y. Fukaya 237 (2004) 21
- Adsorption of thiophene on a Si(001)-2 × 1 surface studied by photoelectron spectroscopy and diffraction, M. Shimomura, Y. Ikejima, K. Yajima, T. Yagi, T. Goto, R. Gunnella, T. Abukawa, Y. Fukuda and S. Kono 237 (2004) 75
- Modification of Sb/Si(001) interface by incorporation of In(4 × 3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(001) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönherr and K.H. Ploog 237 (2004) 181
- Time-resolved core-level photoelectron spectroscopy and reflection high-energy electron diffraction study of surface phase transition on GaAs(001), F. Maeda and Y. Watanabe 237 (2004) 224
- Atomically-controlled GaSb-termination of GaAs surface and its properties, T. Miura, T. Nakai and K. Yamaguchi 237 (2004) 242
- Surface structures of Fe on Mo(110) surface investigated by RHEED, Y. Maehara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488
- A new method to characterize dopant profiles in NMOSFETs using conventional transmission electron microscopy, K. Kawamura, K. Ikeda and M. Terauchi 237 (2004) 621
- Electron emission**
- Monte Carlo study of secondary electron emission from SiO₂ induced by focused gallium ion beams, K. Ohya and T. Ishitani 237 (2004) 606
- Electron microscopy**
- Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida 237 (2004) 156
- Atomically-controlled GaSb-termination of GaAs surface and its properties, T. Miura, T. Nakai and K. Yamaguchi 237 (2004) 242
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387
- Functionalized nanoporous silicas for the immobilization of penicillin acylase, A.S. Maria Chong and X.S. Zhao 237 (2004) 398

- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488
- A new method to characterize dopant profiles in NMOSFETs using conventional transmission electron microscopy, K. Kawamura, K. Ikeda and M. Terauchi 237 (2004) 621
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631
- Recent progress in energy-filtered high energy X-ray photoemission electron microscopy using a Wien filter type energy analyzer, H. Niimi, T. Tsutsumi, H. Matsudaira, T. Kawasaki, S. Suzuki, W.-J. Chun, M. Kato, Y. Kitajima, Y. Iwasawa and K. Asakura 237 (2004) 641

Electron stimulated desorption

- Hydrogen and oxygen behaviors on Porous-Si surfaces observed using a scanning ESD ion microscope, Y. Itoh and K. Ueda 237 (2004) 600
- Development of new X-ray microscopy using a low-energy electron beam, K. Ueda 237 (2004) 636

Epitaxy

- The evolution of the Sb/Si interface at room temperature on the Si(111)-(7 × 7) and the Si(100)-(2 × 1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Strain relaxation of epitaxial CoSi₂ and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(001) and epi-CoSi₂/Si_{0.83}Ge_{0.17}/Si(001) structures, D.O. Shin, M.R. Sardela Jr., S.H. Ban, N.-E. Lee and K.-H. Shim 237 (2004) 139
- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(100), E. Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150
- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(001) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönherr and K.H. Ploog 237 (2004) 181
- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane,

- A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Surface structures of Fe on Mo(110) surface investigated by RHEED, Y. Maehara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316
- Surface study and thickness control of thin Al₂O₃ film on Cu-9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363

Etching

- Etching of polycrystalline copper by oblique injection of argon ion, T. Taguchi, Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa 237 (2004) 321
- Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching, T. Nagai, A. Imanishi and Y. Nakato 237 (2004) 532

Europium

- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387

Ferroelectric properties

- THz time domain spectroscopy of pulsed laser deposited BaTiO₃ thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427

Field emission

- First-principles calculation of field emission from adsorbed atom on metallic electrode, N. Kobayashi, K. Hirose and M. Tsukada 237 (2004) 572

Fullerenes

- Self-assembled organic and fullerene monolayers characterisation by two-colour SFG spectroscopy: a pathway to meet doubly resonant SFG process, C. Humbert, Y. Caudano, L. Dreesen, Y. Sartenauer, A.A. Mani, C. Silien, J.-J. Lemaire, P.A. Thiry and A. Peremans 237 (2004) 462

Gallium

- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Effects of interfacial profiles on quantum levels in $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{GaAs}$ graded spherical quantum dots, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 237 (2004) 266
- Monte Carlo study of secondary electron emission from SiO_2 induced by focused gallium ion beams, K. Ohya and T. Ishitani 237 (2004) 606
- Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers, H. Yamaguchi, S. Miyashita and Y. Hirayama 237 (2004) 649

Gallium antimonide

- Atomically-controlled GaSb-termination of GaAs surface and its properties, T. Miura, T. Nakai and K. Yamaguchi 237 (2004) 242

Gallium arsenide

- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(001) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönher and K.H. Ploog 237 (2004) 181
- First-principles investigations of GaAs(311)A surface reconstruction—failure of the electron counting model, A. Taguchi and K. Shiraishi 237 (2004) 189
- Systematic theoretical investigations of adsorption behavior on the GaAs(001)-c(4 × 4) surfaces, T. Ito, K. Tsutsumida, K. Nakamura, Y. Kangawa, K. Shiraishi, A. Taguchi and H. Kageshima 237 (2004) 194
- Theoretical investigations of adatom behavior on non-planar surfaces with GaAs(n11)A, K. Asano, Y. Kangawa, H. Ishizaki, T. Akiyama, K. Nakamura and T. Ito 237 (2004) 206
- X-ray diffraction study on GaAs(001)-2 × 4 surfaces under molecular-beam epitaxy conditions, M. Takahashi, Y. Yoneda and J. Mizuki 237 (2004) 219
- Time-resolved core-level photoelectron spectroscopy and reflection high-energy electron diffraction study of surface phase transition on GaAs(001), F. Maeda and Y. Watanabe 237 (2004) 224
- Effects of growth sequence on atomic level interfacial structures and characteristics of

- GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Interfacial bonding distribution and energy band structure of $(\text{Gd}_2\text{O}_3)_x - (\text{SiO}_2)_y$ ($x = 0.5$)/GaAs(001) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park 237 (2004) 251
- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokiaaraj, H.S. Djie and T. Mei 237 (2004) 256
- Effects of interfacial profiles on quantum levels in $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{GaAs}$ graded spherical quantum dots, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 237 (2004) 266

Gallium phosphide

- AES and XPS studies of a GaP(001) surface treated by S_2Cl_2 and $\text{P}_2\text{S}_5/(\text{NH}_4)_2\text{S}_x$, K.Z. Liu, Y. Suzuki and Y. Fukuda 237 (2004) 627

Germanium

- Quality of SiO_2 and of SiGe formed by oxidation of $\text{Si}/\text{Si}_{0.7}\text{Ge}_{0.3}$ heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- Strain relaxation of epitaxial CoSi_2 and SiGe layers in cap- $\text{Si}/\text{Si}_{0.83}\text{Ge}_{0.17}/\text{Si}(001)$ and epi- $\text{CoSi}_2/\text{Si}_{0.83}\text{Ge}_{0.17}/\text{Si}(001)$ structures, D.O. Shin, M.R. Sardela Jr., S.H. Ban, N.-E. Lee and K.-H. Shim 237 (2004) 139
- Strain in $\beta\text{-FeSi}_2$ modulated by Ge segregation in solid-phase growth of $[\text{a-Si/a-FeSiGe}]_n$ stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Solvation of $\text{C}_2\text{H}_5\text{OH}$, CH_3CHO , and CH_3COCH_3 molecules on D_2O and CD_3OD -ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514

Gold

- Optical second harmonic spectroscopy of a Au(100) 5 × 20 reconstructed surface, T. Iwai and G. Mizutani 237 (2004) 279
- The growth of Fe, Ni and Co on vicinal Au(111) surfaces, S. Shiraki, H. Fujisawa, M. Nantoh and M. Kawai 237 (2004) 284

Decay of nano-islands on Au(1 0 0) electrode in sulfuric acid solution with Cl^- anions, K. Kubo, N. Hirai and S. Hara

237 (2004) 301

Self-assembled organic and fullerene monolayers characterisation by two-colour SFG spectroscopy: a pathway to meet doubly resonant SFG process, C. Humbert, Y. Caudano, L. Dreesen, Y. Sartenae, A.A. Mani, C. Silien, J.-J. Lemaire, P.A. Thiry and A. Peremans

237 (2004) 462

Recent progress in energy-filtered high energy X-ray photoemission electron microscopy using a Wien filter type energy analyzer, H. Niimi, T. Tsutsumi, H. Matsudaira, T. Kawasaki, S. Suzuki, W.-J. Chun, M. Kato, Y. Kitajima, Y. Iwasawa and K. Asakura

237 (2004) 641

Hafnium

Characterization of $\text{HfO}_2/\text{Si}(0 0 1)$ interface with high-resolution Rutherford backscattering spectroscopy, K. Nakajima, S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang

237 (2004) 416

Halogenides

Hydration of the HCl and NH_3 molecules adsorbed on amorphous water-ice surface, M. Kondo, H. Kawanowa, Y. Gotoh and R. Souda

237 (2004) 509

AES and XPS studies of a $\text{GaP}(0 0 1)$ surface treated by S_2Cl_2 and $\text{P}_2\text{S}_5/(\text{NH}_4)_2\text{S}_x$, K.Z. Liu, Y. Suzuki and Y. Fukuda

237 (2004) 627

Heterostructures

Quality of SiO_2 and of SiGe formed by oxidation of $\text{Si}/\text{Si}_{0.7}\text{Ge}_{0.3}$ heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori

237 (2004) 134

Effects of growth sequence on atomic level interfacial structures and characteristics of $\text{GaInP}/\text{GaAs}/\text{GaInP}$ double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda

237 (2004) 246

Investigations on the blue-shift phenomena in argon plasma intermixed $\text{InGaAs}/\text{InGaAsP}$ quantum well structures, J. Arokiaaraj, H.S. Djie and T. Mei

237 (2004) 256

Hydrides

Dihydride chain formation on a $\text{Si}(1 0 0)-2 \times 1$ -H surface, M. Fujimori, Y. Suwa, S. Heike, Y. Terada and T. Hashizume

237 (2004) 58

Hydrocarbons

Adsorption of cata-condensed aromatics on a $\text{Si}(1 0 0)-2 \times 1$ surface investigated by infrared absorption spectroscopy, K. Okamura, Y. Hosoi, Y. Kimura, H. Ishii and M. Niwano

237 (2004) 439

Investigation of furan on vicinal $\text{Pd}(1 1 1)$ by scanning tunneling microscopy, A. Loui and S. Chiang

237 (2004) 559

Hydrogen

Comparative analysis of the Si dangling bonds saturation by H or D in gas and liquid phases, O. Chikalova-Luzina and T. Matsumoto

237 (2004) 45

Dihydride chain formation on a $\text{Si}(1 0 0)-2 \times 1$ -H surface, M. Fujimori, Y. Suwa, S. Heike, Y. Terada and T. Hashizume

237 (2004) 58

Evolution of surface morphology of Si-trench sidewalls during hydrogen annealing, R. Hiruta, H. Kuribayashi, S. Shimizu, K. Sudoh and H. Iwasaki

237 (2004) 63

Hydrogen interaction with $\text{Si}(1 1 1)\sqrt{3}\times\sqrt{3}$ -B surfaces, M. Yoshimura, K. Watanabe and K. Ueda

237 (2004) 115

Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated $\text{Si}(1 1 1)$ by chemical etching, T. Nagai, A. Imanishi and Y. Nakato

237 (2004) 532

Hydrogen and oxygen behaviors on Porous-Si surfaces observed using a scanning ESD ion microscope, Y. Itoh and K. Ueda

237 (2004) 600

Ice

Hydration of the HCl and NH_3 molecules adsorbed on amorphous water-ice surface, M. Kondo, H. Kawanowa, Y. Gotoh and R. Souda

237 (2004) 509

Indium

Modification of $\text{Sb}/\text{Si}(0 0 1)$ interface by incorporation of $\text{In}(4 \times 3)$ surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama

237 (2004) 99

- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokiaaraj, H.S. Djie and T. Mei 237 (2004) 256
- Effects of interfacial profiles on quantum levels in $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ graded spherical quantum dots, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 237 (2004) 266

Indium arsenide

- Atomic geometry and theoretical scanning tunneling microscopy images of K chains on InAs(110), H. Yi, S. Lee and H. Kim 237 (2004) 200
- Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers, H. Yamaguchi, S. Miyashita and Y. Hirayama 237 (2004) 649

Indium phosphide

- Anisotropy of lateral growth rate in liquid phase epitaxy of InP and its association with kink-step structures on the surface, T. Kochiya, Y. Oyama, K. Suto and J.-i. Nishizawa 237 (2004) 235

Infrared spectroscopy

- Investigation of formation processes of an anodic porous alumina film on a silicon substrate, H. Shiraki, Y. Kimura, H. Ishii, S. Ono, K. Itaya and M. Niwano 237 (2004) 369
- Effects of tetraethoxysilane vapor treatment on the cetyltrimethylammonium bromide-templated silica mesoporous low- k thin film with 3D close-packed array of spherical pores, C.-K. Han, S.-B. Jung and H.-H. Park 237 (2004) 405
- Adsorption of cata-condensed aromatics on a Si(100)- 2×1 surface investigated by infrared absorption spectroscopy, K. Okamura, Y. Hosoi, Y. Kimura, H. Ishii and M. Niwano 237 (2004) 439
- Comparative study between poly(*p*-phenylenevinylene) (PPV) and PPV/SiO₂ nano-composite for interface with aluminum electrode, S. Yoon, H.-J. Choi, J.-K. Yang and H.-H. Park 237 (2004) 450

Interfaces

- Design of electron correlation effects in interfaces and nanostructures, H. Aoki 237 (2004) 2
- The evolution of the Sb/Si interface at room temperature on the Si(111)-(7 \times 7) and the Si(100)-(2 \times 1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Modification of Sb/Si(001) interface by incorporation of In(4 \times 3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation, T. Watanabe, K. Tatsumura and I. Ohdomari 237 (2004) 125
- Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x ($x = 0.5$)/GaAs(001) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park 237 (2004) 251
- Surface structures of Fe on Mo(110) surface investigated by RHEED, Y. Maebara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316
- Characterization of HfO₂/Si(001) interface with high-resolution Rutherford backscattering spectroscopy, K. Nakajima, S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang 237 (2004) 416
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514

Ion bombardment

- Etching of polycrystalline copper by oblique injection of argon ion, T. Taguchi, Y. Yamauchi, Y. Hirohata, T. Hino and M. Nishikawa 237 (2004) 321
- Monte Carlo study of secondary electron emission from SiO₂ induced by focused gallium ion beams, K. Ohya and T. Ishitani 237 (2004) 606
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631

Ion implantation

- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Gholipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy 237 (2004) 332
- Luminescence in Cu-implanted ZnO thin films, I. Sakaguchi, S. Hishita and H. Haneda 237 (2004) 358

Ion scattering

- Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- Characterization of HfO₂/Si(0 0 1) interface with high-resolution Rutherford backscattering spectroscopy, K. Nakajima, S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang 237 (2004) 416
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514

Iron

- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(0 0 1) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönher and K.H. Ploog 237 (2004) 181
- The growth of Fe, Ni and Co on vicinal Au(1 1 1) surfaces, S. Shiraki, H. Fujisawa, M. Nantoh and M. Kawai 237 (2004) 284
- Atomic structure of Fe thin-films on Cu(0 0 1) studied with stereoscopic photography, A.N. Hattori, M. Fujikado, T. Uchida, S. Okamoto, K. Fukumoto, F.Z. Guo, F. Matsui, K. Nakatani, T. Matsushita, K. Hattori and H. Daimon 237 (2004) 311
- Surface structures of Fe on Mo(1 1 0) surface investigated by RHEED, Y. Machara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316

Lead zirconium

- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427

Liquid phase epitaxy

- Anisotropy of lateral growth rate in liquid phase epitaxy of InP and its association with kink-step structures on the surface, T. Kochiya, Y. Oyama, K. Suto and J.-i. Nishizawa 237 (2004) 235

Low energy electron diffraction

- The evolution of the Sb/Si interface at room temperature on the Si(1 1 1)-(7 × 7) and the Si(1 0 0)-(2 × 1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Alloy formation of Ni ultrathin films on Pt(1 1 1) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306

Luminescence

- Atomically-controlled GaSb-termination of GaAs surface and its properties, T. Miura, T. Nakai and K. Yamaguchi 237 (2004) 242
- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr. 237 (2004) 261
- Luminescence in Cu-implanted ZnO thin films, I. Sakaguchi, S. Hishita and H. Haneda 237 (2004) 358
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387

Magnetic measurements

- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(0 0 1) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönher and K.H. Ploog 237 (2004) 181

- Characterization of the electrical and magnetic properties of sub-micron MTJ cells using scanning probe microscope interfaced with an external magnetic field generator, J. Heo, D. Kim, S.B. Park, T. Kim and I. Chung 237 (2004) 593
- Manganese**
- AES and STM investigations of room temperature Mn deposition onto Si(111) at different deposition rates, S. Azatyan, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 105
- Microscopy**
- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336
- Molecular beam epitaxy**
- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(001) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönherr and K.H. Ploog 237 (2004) 181
- Theoretical investigations of adatom behavior on non-planar surfaces with GaAs($n-1$)A, K. Asano, Y. Kangawa, H. Ishizaki, T. Akiyama, K. Nakamura and T. Ito 237 (2004) 206
- X-ray diffraction study on GaAs(001)- 2×4 surfaces under molecular-beam epitaxy conditions, M. Takahashi, Y. Yoneda and J. Mizuki 237 (2004) 219
- Molecular dynamics**
- SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation, T. Watanabe, K. Tatsumura and I. Ohdomari 237 (2004) 125
- Molybdenum**
- Surface structures of Fe on Mo(110) surface investigated by RHEED, Y. Maehara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316
- Oxidation process of Mo₂C(0001) studied by photoelectron spectroscopy, K. Edamoto, M. Sugihara, K. Ozawa and S. Otani 237 (2004) 498
- Monte Carlo simulation**
- Systematic theoretical investigations of adsorption behavior on the GaAs(001)-c(4 \times 4) surfaces, T. Ito, K. Tsutsumida, K. Nakamura, Y. Kangawa, K. Shiraishi, A. Taguchi and H. Kageshima 237 (2004) 194
- Monte Carlo study of secondary electron emission from SiO₂ induced by focused gallium ion beams, K. Ohya and T. Ishitani 237 (2004) 606
- Multilayers**
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- Nanostructures**
- Design of electron correlation effects in interfaces and nanostructures, H. Aoki 237 (2004) 2
- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Decay of nano-islands on Au(100) electrode in sulfuric acid solution with Cl⁻ anions, K. Kubo, N. Hirai and S. Hara 237 (2004) 301
- Investigation of formation processes of anodic porous alumina film on a silicon substrate, H. Shiraki, Y. Kimura, H. Ishii, S. Ono, K. Itaya and M. Niwano 237 (2004) 369
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488
- Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching, T. Nagai, A. Imanishi and Y. Nakato 237 (2004) 532
- Ultra-water-repellent surface: fabrication of complicated structure of SiO₂ nanoparticles by electrostatic self-assembled films, T. Soeno, K. Inokuchi and S. Shiratori 237 (2004) 543
- Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers, H. Yamaguchi, S. Miyashita and Y. Hirayama 237 (2004) 649
- Nickel**
- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(100), E.

- Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150
- The growth of Fe, Ni and Co on vicinal Au(111) surfaces, S. Shiraki, H. Fujisawa, M. Nantoh and M. Kawai 237 (2004) 284
- Alloy formation of Ni ultrathin films on Pt(111) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306
- ### Nitrides
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631
- ### Nitrogen
- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Gholipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy 237 (2004) 332
- Pore structure characterization of large-pore periodic mesoporous organosilicas synthesized with varying SiO₂/template ratios, X. Bao, X.S. Zhao, X. Li and J. Li 237 (2004) 380
- ### Nuclear magnetic resonance
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387
- Functionalized nanoporous silicas for the immobilization of penicillin acylase, A.S. Maria Chong and X.S. Zhao 237 (2004) 398
- ### Optical properties
- The effect of electron bombardment on optical properties of n-type silicon, A.H. Sari, F. Osman, M. Ghoranneviss, H. Hora, R. Hpf and M.R. Hantehzadeh 237 (2004) 161
- ### Organic substances
- Adsorption of thiophene on a Si(001)-2 × 1 surface studied by photoelectron spectroscopy and diffraction, M. Shimomura, Y. Ikejima, K. Yajima, T. Yagi, T. Goto, R. Gunnella, T. Abukawa, Y. Fukuda and S. Kono 237 (2004) 75
- Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo 237 (2004) 393
- Adsorption of cata-condensed aromatics on a Si(100)-2 × 1 surface investigated by infrared absorption spectroscopy, K. Okamura, Y. Hosoi, Y. Kimura, H. Ishii and M. Niwano 237 (2004) 439
- ### Organo metallic vapour deposition
- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- ### Oxidation
- Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- High-resolution photoemission electron spectroscopy study on the oxynitridation of 6H-SiC(0001)-√3 × √3R30° surface, J. Labis, J. Oh, H. Namatame, M. Taniguchi, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 170
- Surface study and thickness control of thin Al₂O₃ film on Cu-9%Al(111) single crystal, Y. Yamauchi, M. Yoshitake and W. Song 237 (2004) 363
- Oxidation process of Mo₂C(0001) studied by photoelectron spectroscopy, K. Edamoto, M. Sugihara, K. Ozawa and S. Otani 237 (2004) 498
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514
- ### Oxides
- Characterization of HfO₂/Si(001) interface with high-resolution Rutherford backscattering spectroscopy, K. Nakajima, S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang 237 (2004) 416

- THz time domain spectroscopy of pulsed laser deposited BaTiO₃ thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421
- Oxygen**
- Hydrogen and oxygen behaviors on Porous-Si surfaces observed using a scanning ESD ion microscope, Y. Itoh and K. Ueda 237 (2004) 600
- Oxynitrides**
- High-resolution photoemission electron spectroscopy study on the oxynitridation of 6H-SiC(0001)- $\sqrt{3}\times\sqrt{3}$ R30° surface, J. Labis, J. Oh, H. Namatame, M. Taniguchi, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 170
- Palladium**
- Investigation of furan on vicinal Pd(111) by scanning tunneling microscopy, A. Loui and S. Chiang 237 (2004) 559
- Phase transitions**
- Structural phase transition and thermal vibration of surface atoms studied by reflection high-energy electron diffraction, Y. Shigeta and Y. Fukaya 237 (2004) 21
- Phosphorus**
- Effects of growth sequence on atomic level interfacial structures and characteristics of GaInP/GaAs/GaInP double heterostructures grown by low-pressure organometallic vapor phase epitaxy, T. Yoshikane, A. Urakami, A. Koizumi, S. Hisadome, M. Tabuchi, K. Inoue, Y. Fujiwara and Y. Takeda 237 (2004) 246
- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokiaaraj, H.S. Djie and T. Mei 237 (2004) 256
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387
- Photo emission**
- Recent progress in energy-filtered high energy X-ray photoemission electron microscopy using a Wien filter type energy analyzer, H. Niimi, T. Tsutsumi, H. Matsudaira, T. Kawasaki, S. Suzuki, W.-J. Chun, M. Kato, Y. Kitajima, Y. Iwasawa and K. Asakura 237 (2004) 641
- Photochemistry**
- Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo 237 (2004) 393
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- Photoelectron spectroscopy**
- Adsorption of thiophene on a Si(001)-2 × 1 surface studied by photoelectron spectroscopy and diffraction, M. Shimomura, Y. Ikejima, K. Yajima, T. Yagi, T. Goto, R. Gunnella, T. Abukawa, Y. Fukuda and S. Kono 237 (2004) 75
- The evolution of the Sb/Si interface at room temperature on the Si(111)-(7 × 7) and the Si(100)-(2 × 1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- High-resolution photoemission electron spectroscopy study on the oxynitridation of 6H-SiC(0001)- $\sqrt{3}\times\sqrt{3}$ R30° surface, J. Labis, J. Oh, H. Namatame, M. Taniguchi, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 170
- Structures of sub-monolayered silicon carbide films, Y. Baba, T. Sekiguchi, I. Shimoyama and K.G. Nath 237 (2004) 176
- Time-resolved core-level photoelectron spectroscopy and reflection high-energy electron diffraction study of surface phase transition on GaAs(001), F. Maeda and Y. Watanabe 237 (2004) 224
- Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x (x = 0.5)/GaAs(001) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park 237 (2004) 251
- Atomic structure of Fe thin-films on Cu(001) studied with stereoscopic photography, A.N. Hattori, M. Fujikado, T. Uchida, S. Okamoto, K. Fukumoto, F.Z. Guo, F. Mat-

- sui, K. Nakatani, T. Matsushita, K. Hattori and H. Daimon 237 (2004) 311
- Valence band structure of the ZnO(10 $\bar{1}$ 0) surface studied by angle-resolved photoemission spectroscopy, K. Sawada, Y. Shirotori, K. Ozawa, K. Edamoto and M. Nakatake 237 (2004) 343
- Room temperature adsorption of NH₃ on Zn-terminated ZnO(0001), T. Hasegawa, Y. Shirotori, K. Ozawa, K. Edamoto and K. Takahashi 237 (2004) 352
- Comparative study between poly(*p*-phenylene-vinylene) (PPV) and PPV/SiO₂ nano-composite for interface with aluminum electrode, S. Yoon, H.-J. Choi, J.-K. Yang and H.-H. Park 237 (2004) 450
- Oxidation process of Mo₂C(0001) studied by photoelectron spectroscopy, K. Edamoto, M. Sugihara, K. Ozawa and S. Otani 237 (2004) 498
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514
- AES and XPS studies of a GaP(001) surface treated by S₂Cl₂ and P₂S₅/(NH₄)₂S_x, K.Z. Liu, Y. Suzuki and Y. Fukuda 237 (2004) 627

Plasma processing

- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokiairaj, H.S. Djie and T. Mei 237 (2004) 256
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488

Platinum

- Alloy formation of Ni ultrathin films on Pt(111) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern 237 (2004) 306
- Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films, K. Tsujimoto, S. Mitani, T. Teraji and T. Ito 237 (2004) 488
- In situ observations of tetraamineplatinum(II) hydroxide adsorption from its aqueous solution on heulandite (010) surface by atomic force microscopy, M. Komiyama, Y.-J. Li and N. Gu 237 (2004) 503
- Local tunneling barrier height imaging of a reconstructed Pt(100) surface, A. Sin-sarp, Y. Yamada, M. Sasaki and S. Yamamoto 237 (2004) 587

Polymers

- Comparative study between poly(*p*-phenylene-vinylene) (PPV) and PPV/SiO₂ nano-composite for interface with aluminum electrode, S. Yoon, H.-J. Choi, J.-K. Yang and H.-H. Park 237 (2004) 450
- Influence of wet chemical treatments on the evolution of epoxy polymer layer surface roughness for use as a build-up layer, S. Siau, A. Vervae, A.V. Calster, I. Swennen and E. Schacht 237 (2004) 456

Positron diffraction

- Precise determination of surface Debye-temperature of Si(111)-7 × 7 surface by reflection high-energy positron diffraction, Y. Fukaya, A. Kawasuso, K. Hayashi and A. Ichimiya 237 (2004) 29
- Kinematical and dynamical analyses of reflection high-energy positron diffraction (RHEPD) patterns from Si(111) 7 × 7 surfaces, K. Hayashi, Y. Fukaya, A. Kawasuso and A. Ichimiya 237 (2004) 34

Pulsed laser deposition

- THz time domain spectroscopy of pulsed laser deposited BaTiO₃ thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421

Quantum effects

- Atomically-controlled GaSb-termination of GaAs surface and its properties, T. Miura, T. Nakai and K. Yamaguchi 237 (2004) 242
- Investigations on the blue-shift phenomena in argon plasma intermixed InGaAs/InGaAsP quantum well structures, J. Arokiairaj, H.S. Djie and T. Mei 237 (2004) 256
- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr. 237 (2004) 261
- Effects of interfacial profiles on quantum levels in In_{0.5}Ga_{0.5}As/GaAs graded spherical quantum dots, C.L.N. Oliveira, J.A.K. Freire, V.N. Freire and G.A. Farias 237 (2004) 266
- Conduction band anisotropy effects on the confined electron states of SiC/SiO₂ quantum dots, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr. 237 (2004) 553

Scanning probe microscopy

- Characterization of the electrical and magnetic properties of sub-micron MTJ cells using scanning probe microscope interfaced with an external magnetic field generator, J. Heo, D. Kim, S.B. Park, T. Kim and I. Chung 237 (2004) 593

Scanning tunneling microscopy

- Dihydride chain formation on a Si(1 0 0)-2 × 1-H surface, M. Fujimori, Y. Suwa, S. Heike, Y. Terada and T. Hashizume 237 (2004) 58
- Modification of Sb/Si(0 0 1) interface by incorporation of In(4 × 3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- AES and STM investigations of room temperature Mn deposition onto Si(111) at different deposition rates, S. Azatyan, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 105
- Hydrogen interaction with Si(1 1 1)√3×√3-B surfaces, M. Yoshimura, K. Watanabe and K. Ueda 237 (2004) 115
- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(1 0 0), E. Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150
- Atomic geometry and theoretical scanning tunneling microscopy images of K chains on InAs(110), H. Yi, S. Lee and H. Kim 237 (2004) 200
- The growth of Fe, Ni and Co on vicinal Au(1 1 1) surfaces, S. Shiraki, H. Fujisawa, M. Nantoh and M. Kawai 237 (2004) 284
- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336
- Local structural change caused by light irradiation on TiO₂ (1 1 0) surface observed by scanning tunneling microscopy, Y.-J. Li, T. Matsumoto, N. Gu and M. Komiyama 237 (2004) 374
- Investigation of furan on vicinal Pd(1 1 1) by scanning tunneling microscopy, A. Loui and S. Chiang 237 (2004) 559
- Elementary processes of vibrationally mediated motions of single adsorbed molecules, H. Ueba 237 (2004) 565
- Kondo effect and surface-state electrons, L. Limot and R. Berndt 237 (2004) 576
- Local tunneling barrier height imaging of a reconstructed Pt(1 0 0) surface, A. Sinsarp, Y. Yamada, M. Sasaki and S. Yamamoto 237 (2004) 587

Schottky barriers

- Energy level broadening of defects causing nonideality in nearly ideal Si Schottky barriers, K. Maeda 237 (2004) 165

Selenides

- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr. 237 (2004) 261

Secondary ion mass spectrometry

- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Gholipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy 237 (2004) 332
- Hydration of the HCl and NH₃ molecules adsorbed on amorphous water-ice surface, M. Kondo, H. Kawanowa, Y. Gotoh and R. Souda 237 (2004) 509

Semi-conductors

- A new method to characterize dopant profiles in NMOSFETs using conventional transmission electron microscopy, K. Kawamura, K. Ikeda and M. Terauchi 237 (2004) 621

Silane

- Effects of tetraethoxysilane vapor treatment on the cetyltrimethylammonium bromide-templated silica mesoporous low-*k* thin film with 3D close-packed array of spherical pores, C.-K. Han, S.-B. Jung and H.-H. Park 237 (2004) 405

Silicides

- Strain relaxation of epitaxial CoSi₂ and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(0 0 1) and epi-CoSi₂/Si_{0.83}Ge_{0.17}/Si(0 0 1) structures, D.O. Shin, M.R. Sardela, S.H. Ban, N.-E. Lee and K.-H. Shim Jr. 237 (2004) 139
- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(1 0 0), E. Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150
- Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida 237 (2004) 156

Silicon

- Structural phase transition and thermal vibration of surface atoms studied by reflection high-energy electron diffraction, Y. Shigeta and Y. Fukaya 237 (2004) 21

- Precise determination of surface Debye-temperature of Si(111)- 7×7 surface by reflection high-energy positron diffraction, Y. Fukaya, A. Kawasuso, K. Hayashi and A. Ichimiya 237 (2004) 29
- Kinematical and dynamical analyses of reflection high-energy positron diffraction (RHEPD) patterns from Si(111)- 7×7 surfaces, K. Hayashi, Y. Fukaya, A. Kawasuso and A. Ichimiya 237 (2004) 34
- Structure of the Si(113) surface studied by surface X-ray diffraction, Y. Mizuno, K. Akimoto, T. Aoyama, H. Suzuki, H. Nakahara, A. Ichimiya, K. Sumitani, T. Takahashi, X. Zhang, H. Sugiyama and H. Kawata 237 (2004) 40
- Comparative analysis of the Si dangling bonds saturation by H or D in gas and liquid phases, O. Chikalova-Luzina and T. Matsu-moto 237 (2004) 45
- Dihydride chain formation on a Si(100)- 2×1 -H surface, M. Fujimori, Y. Suwa, S. Heike, Y. Terada and T. Hashizume 237 (2004) 58
- Evolution of surface morphology of Si-trench sidewalls during hydrogen annealing, R. Hiruta, H. Kuribayashi, S. Shimizu, K. Sudoh and H. Iwasaki 237 (2004) 63
- Adsorption of thiophene on a Si(001)- 2×1 surface studied by photoelectron spectroscopy and diffraction, M. Shimomura, Y. Ikejima, K. Yajima, T. Yagi, T. Goto, R. Gunnella, T. Abukawa, Y. Fukuda and S. Kono 237 (2004) 75
- The evolution of the Sb/Si interface at room temperature on the Si(111)-(7×7) and the Si(100)-(2×1) reconstructed surfaces, S.M. Shivaprasad, V.K. Paliwal and A. Chaudhuri 237 (2004) 93
- Modification of Sb/Si(001) interface by incorporation of In(4×3) surface reconstruction, D.V. Gruznev, K. Ohmura, M. Mori, T. Tambo, V.G. Lifshits and C. Tatsuyama 237 (2004) 99
- AES and STM investigations of room temperature Mn deposition onto Si(111) at different deposition rates, S. Azatyan, M. Hirai, M. Kusaka and M. Iwami 237 (2004) 105
- Hydrogen interaction with Si(111)- $\sqrt{3} \times \sqrt{3}$ -B surfaces, M. Yoshimura, K. Watanabe and K. Ueda 237 (2004) 115
- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits 237 (2004) 119
- SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation, T. Watanabe, K. Tatsumura and I. Ohdomari 237 (2004) 125
- Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori 237 (2004) 134
- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- Influence of C incorporation on the initial growth of epitaxial NiSi₂ on Si(100), E. Okada, O. Nakatsuka, S. Oida, A. Sakai, S. Zaima and Y. Yasuda 237 (2004) 150
- Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida 237 (2004) 156
- The effect of electron bombardment on optical properties of n-type silicon, A.H. Sari, F. Osman, M. Ghoranneviss, H. Hora, R. Hpf and M.R. Hantehzadeh 237 (2004) 161
- Energy level broadening of defects causing nonideality in nearly ideal Si Schottky barriers, K. Maeda 237 (2004) 165
- Functionalized nanoporous silicas for the immobilization of penicillin acylase, A.S. Maria Chong and X.S. Zhao 237 (2004) 398
- Characterization of HfO₂/Si(001) interface with high-resolution Rutherford backscattering spectroscopy, K. Nakajima, S. Joumori, M. Suzuki, K. Kimura, T. Osipowicz, K.L. Tok, J.Z. Zheng, A. See and B.C. Zhang 237 (2004) 416
- Adsorption of cata-condensed aromatics on a Si(100)- 2×1 surface investigated by infrared absorption spectroscopy, K. Okamura, Y. Hosoi, Y. Kimura, H. Ishii and M. Niwano 237 (2004) 439
- Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda 237 (2004) 514
- Scratch induced nano-wires acting as a macro-pattern for formation of well-ordered step structures on H-terminated Si(111) by chemical etching, T. Nagai, A. Imanishi and Y. Nakato 237 (2004) 532
- Hydrogen and oxygen behaviors on Porous-Si surfaces observed using a scanning ESD ion microscope, Y. Itoh and K. Ueda 237 (2004) 600
- Sample holder assembly covering a wide range of temperatures for surface X-ray diffraction, H. Tajiri, K. Sumitani, S. Nakatani, T. Takahashi, K. Akimoto, H. Sugiyama, X. Zhang and H. Kawata 237 (2004) 645

Silicon carbide

- High-resolution photoemission electron spectroscopy study on the oxynitridation of 6H-SiC(0001)- $\sqrt{3} \times \sqrt{3}$ surface, J. Labis,

- J. Oh, H. Namatame, M. Taniguchi, M. Hirai, M. Kusaka and M. Iwami
Structures of sub-monolayered silicon carbide films, Y. Baba, T. Sekiguchi, I. Shimoyama and K.G. Nath
Conduction band anisotropy effects on the confined electron states of SiC/SiO₂ quantum dots, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr.

237 (2004) 170

237 (2004) 176

237 (2004) 553

Silicon oxide

- SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation, T. Watanabe, K. Tatsumura and I. Ohdomari
Quality of SiO₂ and of SiGe formed by oxidation of Si/Si_{0.7}Ge_{0.3} heterostructure using atomic oxygen at 400 °C, H. Nohira, T. Kuroiwa, M. Nakamura, Y. Hirose, J. Mitsui, W. Sakai, K. Nakajima, M. Suzuki, K. Kimura, K. Sawano, K. Nakagawa, Y. Shiraki and T. Hattori
Interfacial bonding distribution and energy band structure of (Gd₂O₃)_{1-x}(SiO₂)_x (x = 0.5)/GaAs (0 0 1) system, J.-K. Yang, M.-G. Kang, W.S. Kim and H.-H. Park
Pore structure characterization of large-pore periodic mesoporous organosilicas synthesized with varying SiO₂/template ratios, X. Bao, X.S. Zhao, X. Li and J. Li
Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo
Effects of tetraethoxysilane vapor treatment on the cetyltrimethylammonium bromide-templated silica mesoporous low-*k* thin film with 3D close-packed array of spherical pores, C.-K. Han, S.-B. Jung and H.-H. Park
Solvation of C₂H₅OH, CH₃CHO, and CH₃COCH₃ molecules on D₂O and CD₃OD-ice surfaces, H. Kawanowa, M. Kondo, T. Shibata, Y. Gotoh and R. Souda
Ultra-water-repellent surface: fabrication of complicated structure of SiO₂ nanoparticles by electrostatic self-assembled films, T. Soeno, K. Inokuchi and S. Shiratori
Conduction band anisotropy effects on the confined electron states of SiC/SiO₂ quantum dots, J.S. de Sousa, V.N. Freire and E.F. da Silva Jr.
Monte Carlo study of secondary electron emission from SiO₂ induced by focused gallium ion beams, K. Ohya and T. Ishitani

237 (2004) 125

237 (2004) 134

237 (2004) 251

237 (2004) 380

237 (2004) 393

237 (2004) 405

237 (2004) 514

237 (2004) 543

237 (2004) 553

237 (2004) 606

Silver

- Stability and electric conductivity of Si-metal surface reconstructions during amorphous Si deposition, S.V. Ryjkov, M.V. Lavrinaitis, D.A. Tsukanov and V.G. Lifshits
Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida
Alloy formation of Ni ultrathin films on Pt(1 1 1) with Ag buffer layers, H.Y. Ho, C.W. Su, Y.W. Chu and C.S. Shern
Self-assembled organic and fullerene monolayers characterisation by two-colour SFG spectroscopy: a pathway to meet doubly resonant SFG process, C. Humbert, Y. Caudano, L. Dreesen, Y. Sartenauer, A.A. Mani, C. Silien, J.-J. Lemaire, P.A. Thiry and A. Peremans
Kondo effect and surface-state electrons, L. Limot and R. Berndt

237 (2004) 119

237 (2004) 156

237 (2004) 306

237 (2004) 462

237 (2004) 576

Steel

- Comparison of experimental and theoretical results of nitrogen implantation in AISI 304 stainless steel, S.H. Hoji Hosseini Gazestani, M. Ghelipour Shahraki, M.R. Hantehzadeh, M. Ghoranneviss and A. Shokouhy
Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe

237 (2004) 332

237 (2004) 631

Sulphides

- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr.
AES and XPS studies of a GaP(0 0 1) surface treated by S₂Cl₂ and P₂S₅/(NH₄)₂S₂, K.Z. Liu, Y. Suzuki and Y. Fukuda

237 (2004) 261

237 (2004) 627

Super conductivity

- Design of electron correlation effects in interfaces and nanostructures, H. Aoki

237 (2004) 2

Superlattices

- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr.

237 (2004) 261

Surface diffraction

- Decay of nano-islands on Au(1 0 0) electrode in sulfuric acid solution with Cl^- anions, K. Kubo, N. Hirai and S. Hara 237 (2004) 301

Surface morphology

- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336

Surface roughness

- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336
- Influence of wet chemical treatments on the evolution of epoxy polymer layer surface roughness for use as a build-up layer, S. Siau, A. Vervaeke, A.V. Calster, I. Swennen and E. Schacht 237 (2004) 456

Surface structure

- Structure of the Si(1 1 3) surface studied by surface X-ray diffraction, Y. Mizuno, K. Akimoto, T. Aoyama, H. Suzuki, H. Nakahara, A. Ichimiya, K. Sumitani, T. Takahashi, X. Zhang, H. Sugiyama and H. Kawata 237 (2004) 40
- Surface structures of Fe on Mo(1 1 0) surface investigated by RHEED, Y. Maehara, A. Yamada, H. Kawanowa and Y. Gotoh 237 (2004) 316
- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336
- Local structural change caused by light irradiation on TiO_2 (1 1 0) surface observed by scanning tunneling microscopy, Y.-J. Li, T. Matsumoto, N. Gu and M. Komiyama 237 (2004) 374
- Sample holder assembly covering a wide range of temperatures for surface X-ray diffraction, H. Tajiri, K. Sumitani, S. Nakatani, T. Takahashi, K. Akimoto, H. Sugiyama, X. Zhang and H. Kawata 237 (2004) 645

Tantalum

- Recent progress in energy-filtered high energy X-ray photoemission electron microscopy using a Wien filter type energy analyzer, H. Niimi, T. Tsutsumi, H. Matsudaira, T. Kawasaki, S. Suzuki, W.-J. Chun, M. Kato, Y. Kitajima, Y. Iwasawa and K. Asakura 237 (2004) 641

Thin films

- Effect of an Ag buffer layer on a Cu/Ag/Si system, M. Yukawa, H. Kitagawa and S. Iida 237 (2004) 156
- Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(0 0 1) substrates, J. Herfort, W. Braun, A. Trampert, H.-P. Schönherr and K.H. Ploog 237 (2004) 181
- THz time domain spectroscopy of pulsed laser deposited BaTiO_3 thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631

Time-of-flight techniques

- Development of new X-ray microscopy using a low-energy electron beam, K. Ueda 237 (2004) 636

Titanium

- THz time domain spectroscopy of pulsed laser deposited BaTiO_3 thin films, M. Misra, K. Kotani, T. Kiwa, I. Kawayama, H. Murakami and M. Tonouchi 237 (2004) 421
- Characterization of TiN thin films subjected to nanoindentation using focused ion beam milling, L.W. Ma, J.M. Cairney, M.J. Hoffman and P.R. Munroe 237 (2004) 631

Titanium oxide

- Local structural change caused by light irradiation on TiO_2 (1 1 0) surface observed by scanning tunneling microscopy, Y.-J. Li, T. Matsumoto, N. Gu and M. Komiyama 237 (2004) 374
- Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo 237 (2004) 393
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427

Tunneling

- Local tunneling barrier height imaging of a reconstructed Pt(1 0 0) surface, A. Sinsarp, Y. Yamada, M. Sasaki and S. Yamamoto 237 (2004) 587

- Characterization of the electrical and magnetic properties of sub-micron MTJ cells using scanning probe microscope interfaced with an external magnetic field generator, J. Heo, D. Kim, S.B. Park, T. Kim and I. Chung 237 (2004) 593
- Water**
- Hydration of the HCl and NH₃ molecules adsorbed on amorphous water-ice surface, M. Kondo, H. Kawanowa, Y. Gotoh and R. Souda 237 (2004) 509
- Work function**
- Local tunneling barrier height imaging of a reconstructed Pt(1 0 0) surface, A. Sinsarp, Y. Yamada, M. Sasaki and S. Yamamoto 237 (2004) 587
- X-ray absorption**
- Structures of sub-monolayered silicon carbide films, Y. Baba, T. Sekiguchi, I. Shimoyama and K.G. Nath 237 (2004) 176
- Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo 237 (2004) 393
- X-ray diffraction**
- Structure of the Si(1 1 3) surface studied by surface X-ray diffraction, Y. Mizuno, K. Akimoto, T. Aoyama, H. Suzuki, H. Nakahara, A. Ichimiya, K. Sumitani, T. Takahashi, X. Zhang, H. Sugiyama and H. Kawata 237 (2004) 40
- SiO₂/Si interface structure and its formation studied by large-scale molecular dynamics simulation, T. Watanabe, K. Tatsumura and I. Ohdomari 237 (2004) 125
- Strain relaxation of epitaxial CoSi₂ and SiGe layers in cap-Si/Si_{0.83}Ge_{0.17}/Si(0 0 1) and epi-CoSi₂/Si_{0.83}Ge_{0.17}/Si(0 0 1) structures, D.O. Shin, M.R. Sardela Jr., S.H. Ban, N.-E. Lee and K.-H. Shim 237 (2004) 139
- Strain in β -FeSi₂ modulated by Ge segregation in solid-phase growth of [a-Si/a-FeSiGe]_n stacked structure, T. Sadoh, Y. Murakami, A. Kenjo, T. Enokida, T. Yoshitake, M. Itakura and M. Miyao 237 (2004) 146
- X-ray diffraction study on GaAs(0 0 1)-2 \times 4 surfaces under molecular-beam epitaxy conditions, M. Takahashi, Y. Yoneda and J. Mizuki 237 (2004) 219
- Pore structure characterization of large-pore periodic mesoporous organosilicas synthesized with varying SiO₂/template ratios, X. Bao, X.S. Zhao, X. Li and J. Li 237 (2004) 380
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387
- Efficient adsorption and photocatalytic degradation of organic pollutants diluted in water using fluoride-modified hydrophobic mesoporous silica, H. Yamashita, K. Maekawa, H. Nakao and M. Anpo 237 (2004) 393
- Effects of tetraethoxysilane vapor treatment on the cetyltrimethylammonium bromide-templated silica mesoporous low- k thin film with 3D close-packed array of spherical pores, C.-K. Han, S.-B. Jung and H.-H. Park 237 (2004) 405
- Stacking effect on the ferroelectric properties of PZT/PLZT multilayer thin films formed by photochemical metal-organic deposition, H.-H. Park, H.-H. Park and R.H. Hill 237 (2004) 427
- Sample holder assembly covering a wide range of temperatures for surface X-ray diffraction, H. Tajiri, K. Sumitani, S. Nakatani, T. Takahashi, K. Akimoto, H. Sugiyama, X. Zhang and H. Kawata 237 (2004) 645
- X-ray microscopy**
- Development of new X-ray microscopy using a low-energy electron beam, K. Ueda 237 (2004) 636
- X-ray scattering**
- Functionalized nanoporous silicas for the immobilization of penicillin acylase, A.S. Maria Chong and X.S. Zhao 237 (2004) 398
- X-ray spectroscopy**
- Doping of europium in the pores of surface-modified SBA-15, C. Gu, P.A. Chia and X.S. Zhao 237 (2004) 387
- Zeolites**
- In situ observations of tetraamineplatinum(II) hydroxide adsorption from its aqueous solution on heulandite (0 1 0) surface by atomic force microscopy, M. Komiyama, Y.-J. Li and N. Gu 237 (2004) 503
- Zinc**
- Interface properties in ZnSe/ZnS based strained superlattices and quantum wells, F.F. Maia Jr., J.A.K. Freire, V.N. Freire, G.A. Farias and E.F. da Silva Jr. 237 (2004) 261

Zinc oxide

- Atomic-scale properties of low-index ZnO surfaces, U. Diebold, L.V. Koplitz and O. Dulub 237 (2004) 336
- Valence band structure of the ZnO(10 $\bar{1}$ 0) surface studied by angle-resolved photoemission spectroscopy, K. Sawada, Y. Shirotori, K. Ozawa, K. Edamoto and M. Nakatake 237 (2004) 343
- Room temperature adsorption of NH₃ on Zn-terminated ZnO(0001), T. Hasegawa, Y. Shirotori, K. Ozawa, K. Edamoto and K. Takahashi 237 (2004) 352
- Luminescence in Cu-implanted ZnO thin films, I. Sakaguchi, S. Hishita and H. Haneda 237 (2004) 358